NARASARAOPETA ENGINEERING COLLEGE (AUTONOMOUS)



APPLIED PHYSICS MATERIAL

/	
	NAME:
	ROLL NO:
	BRANCH: SECTION:
	YEAR OF STUDY:



Applied Physics (ECE, EEE, CSE, IT&CAI)

Code:	Applied Physics (ECE-EEE-CSE-IT&CAI)							
I/II SEMESTER	4	0	0	30	70	100	3	
I B.TECH	L	Т	Р	MARKS	MARKS	MARKS	CREDITS	
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COURSE OBJECTIVES:

- To impart knowledge in basic concepts of wave optics, fiber optics, properties of solid crystal materials and magnetic materials, acoustics, superconductors.
- To familiarize the applications of materials relevant to engineering field.

COURSE OUTCOMES:

After successful completion of this course, the students will be able to:

- **CO 1:** Utilise the experimental evidence of wave nature of light and interference in thin films, Diffraction grating and Polaraisation in various fields. **(K3)**
- CO 2: Analyse and understand various types of lasers & optical fibers.(K4)
- CO 3: Identify the crystal structures and XRD techniques. (K3).
- CO 4: Apply the magnetic materials in engineering field. (K3)
- CO 5: Identify the various applications of semiconductors in engineering field. (K3)

UNIT-I

Interference & Diffraction: Introduction -Interference in thin films by reflection – Newton's rings, introduction to diffraction – difference between Fresnel's and Fraunhofer diffraction - Fraunhofer diffraction at single slit (qualitative) - Diffraction grating.

Polarization: Introduction – Types of Polarization – Double refraction – Nicol's prism-Quarter wave plate and Half Wave plate - Applications

UNIT-II

Lasers: Introduction – Characteristics of lasers – Spontaneous and Stimulated emission of radiation – Population inversion – Ruby laser – Helium Neon laser-Applications.

Fiber Optics: Introduction- Basic Structure and Principle of optical fiber - Acceptance angle – Acceptance cone - Numerical Aperture-Applications.



UNIT-III

Crystallography : Introduction – Space lattice – Basis – Unit Cell – Lattice parameters – Bravais lattices – Crystal systems – Structures and packing fractions of SC,BCC and FCC.

X-Ray Diffraction: Directions and planes in crystals – Miller indices – Separation between successive (h k l) planes – Bragg's law.

UNIT-IV

Electromagnetic Fields: Gauss divergence theorem - Stokes theorem (Quantitative) – Fundamental laws of electromagnetism – Maxwell's Electromagnetic Equations.

Magnetic materials: Magnetic Susceptibility- Magnetic permeability –Classification of Magnetic materials – Dia, Para, and Ferro – Hysteresis Loop- Soft and Hard magnetic materials – Applications- Superconductivity- Properties, Meissner effect - Type-I and Type-II super conductors.

UNIT-V

Quantum Mechanics: Introduction –de-Broglie's concept of Matter waves – Physical significance of wave function - Schrodinger Time Independent wave equations – Particle in a one dimensional potential box.

Semiconductor Physics: Origin of energy band formation in solids- classification of materials into conductors, semiconductors and insulators, Intrinsic and Extrinsic semiconductor- Hall Effect.

TEXT BOOKS:

- 1. A.J. Dekker, "Solid state Physics", ISBN 10: 0333918339 / ISBN 13: 9780333918333, Mc Millan India Ltd, First edition, 2000.
- 2. M.N. Avadhanulu & P.G. Kshirasagar, "A text book of Engineering Physics", ISBN 81-219-0817-5, S. Chand publications, First Edition, 2011.
- 3. P. K. Palanisamy, "Engineering Physics", ISBN: 9788183714464, Scitech Publishers, 4th Edition, 2014
- M.R. Srinivasan, "Engineering Physics", ISBN978-81-224-3636-5, New Age international publishers, 2nd Edition, 2014



REFERENCE BOOKS:

1. Charles Kittle, "Introduction to solid state physics" ISBN: 9788126578436, Willey India Pvt.Ltd, 5^{TH} edition, 2012.

2. M.Arumugam, "Applied Physics", ISBN: 81-89638-01-7, Anuradha Agencies, 4th edition, 2013.

3. D.K.Bhattacharya, "Engineering Physics", ISBN: 0198065426, 9780198065425, Oxford University press, 2nd edition, 2010.

- 4. Sanjay D Jain and Girish G Sahasrabudhe "Engineering Physics", University Press ISBN: 8173716781,1st edition, 2010.
- 5. B.K.Pandey & S. Chaturvedi "Engineering Physics" ISBN: 8131517616, Cengage Learning, 1st edition, 2012.

Web References:

- 1. http://link.springer.com/physics
- 2. http://www.thphys.physics.ox.ac.uk
- 3. http://www.sciencedirect.com/science
- 4. http://www.e-booksdirectory.com

E-Books:

- 1. http://www.peaceone.net/basic/Feynman
- 2. <u>http://physicsdatabase.com/free-physics-books</u>
- 3. http://www.damtp.cam.ac.uk/user/tong/statphys/sp.pdf
- 4. http://www.freebookcentre.net/Physics/Solid-State-Physics-Books.html





Model Question Paper-I

Subject Code: R20CC1205

APPLIED PHYSICS (Common to ECE)

Time: 3 Hrs

Max. Marks: 70

Note: Answer All FIVE Questions All Questions Carry Equal Marks

S. No		Question	Cognitive Level	CO	Marks
	Α	i) Describe the principle and formation of Newton's Rings and give a method to determine wavelength of monochromatic light.	K1	1	10
1		ii) Newton's Rings are observed in reflected light of wavelength 5900A°. The diameter of the 10 th dark ring is 0.5 cm. Estimate the radius of curvature of the lens.	К2	1	4
	В	i) Describe the conditions for primary and secondary maxima in Fraunhofer diffraction due to a single slit and derive an expression for width of central maxima.	K1	1	10
		ii) Evaluate the thickness of half wave plate and quarter wave plate when the wavelength is $5890A^{\circ}$. $\mu 0=1.55$ and $\mu e=1.54$	К5	1	4
	A	i) With the help of suitable diagram explain the principle, construction and working of He-Ne laser and give any four applications of lasers.	K4	2	10
		ii) Distinguish between spontaneous and stimulated emission	K2	2	4
2	B	i). Define acceptance angle for an optical fiber? Obtain mathematical expression for acceptance angle and numerical aperture.	K1	2	10
		ii) Evaluate the acceptance angle and the numerical aperture of a given optical fiber, if the refractive indices of core and cladding are 1.562 and 1.497 respectively.	К5	2	4
	Α	i)Explain the relation between SC, BCC, FCC structures in terms of coordination number and atomic paking fraction	К5	3	8
		ii) Describe the seven crystal system on the basis of lattice parameters with neat diagram	К5	3	6
3		i). Derive an expression for the inter planar spacing between two adjacent planes of miller indices (hkl) in a cubic lattice.	K1	3	10
	R	ii). A beam of x-rays of wavelength 0.071 nm is diffracted by (110) plane of rock salt with lattice constant of 0.28nm estimate the glancing angle for the second order diffraction.	К2	3	4
4	Α	i) State and prove Gauss and Stokes Theorems	K1	4	8
		ii) Write the Maxwell's electromagnetic equations	K6	4	6

	B	i) Explain the classification of magnetic materials	K2	4	10
		ii) Explain Type-I and Type-II super conductors.	K2	4	4
	A	i) Write the Schrodinger equation for a particle in ine dimensional box; solve the Eigen values and Eigen functions.	K1	5	10
5		ii) Evaluate the energy of an electron moving in one dimension in an infinitely high potential box of width 1 A° (Mass of the electron is 9.1x10-31 kg and h=6.63x10-34 Js.	K5	5	4
	B	i) Describe the Hall effect and derive the expression for Hall coefficient.	K1	5	10
		ii) Distinguish between intrinsic and extrinsic semiconductors with suitable examples.	K2	5	4



Model Question Paper-II

Subject Code: R20CC1205

APPLIED PHYSICS (Common to ECE)

Time: 3 Hrs

Max. Marks: 70

Note: Answer All FIVE Questions All Questions Carry Equal Marks

S. No		Question	Cognitive	CO	Marks
		i) Derive the cosine law for the thin films in reflected systems are show that the interference patterns of reflected and transmitted systems are complementary.	K1	1	10
1	A	ii) A parallel beam of light of wavelength 5890A° is incident on a thin glass plate with refractive index 1.5, the angle of refractive index 1.5; the angle of refraction is 60°. Estimate the thickness of the glass plate which will appear dark in reflection and transmission.	К2	1	4
	В	i) Describe the conditions for primary and secondary maxima in Fraunhofer diffraction due to a single slit and derive an expression for width of central maxima.	K1	1	10
		ii) Evaluate the thickness of half wave plate and quarter wave plate when the wavelength is $5890A^{\circ}$. $\mu 0=1.58$ and $\mu e=1.54$	К5	1	4
	A	i) With the help of suitable diagram explain the principle, construction and working of He-Ne laser and give any four applications of lasers.	K4	2	10
		ii) Explain the characteristics of Lasers.	K5	2	4
2	В	i). Define acceptance angle for an optical fiber? Obtain mathematical expression for acceptance angle and numerical aperture.	K1	2	10
		ii) Evaluate the acceptance angle and the numerical aperture of a given optical fiber, if the refractive indices of core and cladding are 1.562 and 1.497 respectively.	К5	2	4
	A	i)Explain the relation between SC, BCC, FCC structures in terms of coordination number and atomic paking fraction	K5	3	10
		ii) copper has FCC structure and its atomic radius is 1.278 A°, evaluate its free volume per unit cell.	K5	3	4
3		i). Define are Miller indices? What are the important features of miller indices?	K1	3	10
	B	ii). A beam of x-rays of wavelength 0.071 nm is diffracted by (110) plane of rock salt with lattice constant of 0.28 nm estimate the glancing angle for the second order diffraction.	K2	3	4
4	A	iii)State and prove Gauss and Stokes Theorems.	K1	4	8

		iv) Write the Maxwell's electromagnetic equations.	K6	4	6
	B	i) Explain the classification of magnetic materials.	K2	4	10
		ii) Explain Type-I and Type-II super conductors.	K2	4	4
	A	i) Define matter waves? Derive Schrodinger's time independent wave equation.	K1	5	10
5		ii) Evaluate the energy of an electron moving in one dimension in an infinitely high potential box of width 1 A° (Mass of the electron is 9.1x10-31 kg and h=6.63x10-34 Js.	K5	5	4
	В	i) Describe the formation of energy bands in solids and classify solids into conductors, semiconductors and insulators.	K1	5	10
		ii) Distinguish between intrinsic and extrinsic semiconductors with suitable examples.	K2	5	4

<u>UNIT – I</u>

Chapter – I: Interference & Diffraction.

Chapter – II: Polarization

Course Outcome:

CO 1: Utilise the experimental evidence of wave nature of light and interference in thin films, Diffraction grating and Polaraisation in various fields. (K3)

<u>APPLIED PHYSICS</u> <u>UNIT-I</u>

INTERFERENCE

Introduction:-

Interference of light was first demonstrated by Thomos Young in 1802.

- Many observations in our day to day life are due to interference of light.
 - Ex: Multiple colors on soap bubbles

Thin layers of floating oil when viewed in sunlight.

- Interference is based on the principle of superposition of waves.
- Interference is the optical phenomenon in which brightness and darkness images are produced by two exactly similar light waves meeting.

Definition:-

When light waves of same frequency and having constant phase difference, the resulting the superposition of two light waves is called interference.



- The pattern of bright and dark fringes (images) produced is called interference patterns.
- These interference is of two types, they are
 - 1. Constructive Interference
 - 2. Destructive Interference

Constructive Interference:-

When the resultant amplitude is the sum of the amplitudes due to two light waves is known as Constructive Interference.

Destructive Interference:-

When the resultant amplitude is equal to the difference of two amplitudes is known as Destructive Interference.

Conditions for interference fringes:-

- 1. The two light sources emitting light waves should be coherent.
- 2. The two sources must emit continuous light waves of same wavelength and frequency.
- 3. The sources must be monochromatic.
- 4. The sources should be narrow, i.e. they must be small.
- 5. To view interference fringes, the background should be dark.
- 6. The amplitude of light waves should be equal or nearly equal.

Interference due to thin films:-

When white light is reflected by thin films like soap bubbles, oil layers on water and oxide layers on metal surface a variety of color could be seen. This is due to interference between light waves reflected by the front and back surface of these films.

A phase change of π (or) a path difference of " $\lambda/2$ " is introduced when light travel from rarer to denser medium. But no changes can occur when light travel from denser to rarer medium.

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Explanation:-

Consider a thin film of thickness "t" and refractive index " μ " bounded by two planes surface XY and RS. A ray of light AB incident on the surface XY at an angle "i" is partly reflected along BC and partly refracted into the medium along BD making



an angle of refraction "r" at D, it is again partly reflected along DE-inside, the medium and partly refracted out of the medium along DK. Similarly reflections and refractions occur as shown in figure.

Interference in reflected system:-

Draw EP perpendicular to BC. Now BC and EF are the coherent waves which are going to interference, path difference between BC and EF are

Path difference =
$$\mu$$
 (BD+DE) – BP
Now consider $\Delta le BQD$, $\cos r = \frac{DQ}{BD} = \frac{t}{BD} \Rightarrow BD = \frac{t}{\cos r}$
 $\Rightarrow BD = DE = \frac{t}{\cos r}$
Now consider $\Delta le BQD$, $\tan r = \frac{BQ}{DQ} = \frac{BQ}{DQ} \Rightarrow BQ = t \cdot \tan r$
 $\Rightarrow BQ = QE = t \cdot \tan r$
 $\therefore \mu (BD+DE) = \mu \left(\frac{t}{\cos r} + \frac{t}{\cos r}\right) = \mu \left(\frac{2t}{\cos r}\right) = \frac{2\mu t}{\cos r}$
Now consider $\Delta le BEP$ $\sin i = \frac{BP}{BE}$
 $\Rightarrow BP = BE \sin i$
 $= (BQ+QE) \sin i$
 $BP = (2t \tan r) \sin i = 2t \cdot \frac{\sin r}{\cos r} \cdot \sin i \chi \frac{\sin r}{\sin r}$
 $= 2t \cdot \frac{\sin^2 r}{\cos r} \chi \frac{\sin i}{\sin r} - (\text{from Snell's Law } \mu = \frac{\sin i}{\sin r})$
 $= 2\mu t \frac{\sin^2 r}{\cos r}$
 $\therefore Path difference = \mu (BD+DE) - BP$
 $= \frac{2\mu t}{\cos r} - 2\mu t \frac{\sin^2 r}{\cos r}$
 $= 2\mu t \cos^2 r$
 $= 2\mu t \cos^2 r$
 $\therefore Path difference = 2\mu t \cos r$

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Case (i):- Bright Band

If the film will appear bright (or) constructive interference will form, if the path difference is

 $2\mu t \cos r = (2n+1) \lambda/2$ - where $n = 0, 1, 2, 3 \dots$

Case (ii):- Dark Band

If the film will appear dark (or) destructive interference will form, if the path difference is

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2\mu t \cos r = (2n) \lambda/2 = n\lambda - where n=1, 2, 3 ...
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Newton's Rings:-

Experimental arrangement:-

The experimental arrangement of obtaining Newton's rings is shown in below figure.

Let "L" is Plano convex lens of radius of large curvature. This lens with its convex surface is placed on a glass plate "P". The lens "L" contact with the plate P at point "O". A monochromatic source such as sodium lamp fall on a glass plate "G" held at an angle 45° with the vertical. The glass plate "G" reflects normally a part of incident light towards the lens "L" and glass plate "P". A part of incident light is reflected by the curved surface of the lens "L" and a part is transmitted which is reflected back from the plane surface of the plate "P". These two reflected rays interfere and give rise to an interference pattern in the form



of circular rings. It can be seen with a microscope. This phenomenon was first described by Newton, that it why the rings are known as Newton's rings.

Explanation:-

The formation of Newton's rings can be explained with the help of the figure. AB is a monochromatic ray of light which falls on the system. A part of light is reflected at "C", which goes out in the form of ray-1 without any phase. The other part of light is refracted along CD. At point "D" it is again reflected and goes out in the form of ray-2 with a phase of π . The reflected rays 1 and 2 are in a position



to produce interference pattern and appears as a bright and dark rings.

As the rings are observed in the reflected light, the path difference between them is $(2\mu t \cos r + \lambda/2)$.

It µ=1, r=0

Then, the path difference = $(2t+\lambda/2)$

At the point of contact t=0, then the path difference is $\lambda/2$.

Condition for Bright ring is:-

$$2t + \lambda/2 = n\lambda$$

 $2t = n\lambda - \lambda/2$
 $2t = \frac{2n\lambda - \lambda}{2}$
 $2t = \frac{(2n-1)\lambda}{2}$, where n=1,2,3,....

Condition for Dark ring is:-

$$2t + \lambda/2 = (2n+1)\lambda/2$$

$$2t = \frac{2n\lambda}{2} + \frac{\lambda}{2} - \frac{\lambda}{2}$$

$$2t = n\lambda, \text{ where } n = 0, 1, 2, 3, \dots$$

Calculating the diameter of the ring:-

Let LOL' be the lens placed on the glass plate "P". The curved surface LOL' is part of the spherical surface with the centre at "C". Let 'R' be the radius of curvature and 'r' be the radius of Newton's rings corresponding to constant film thickness "t".

From the property of the circle



NQ X NS = NO X ND

$$r x r = t x (2R - t)$$

 $r^2 = 2tR - t^2 2tR$
 $r^2 = 2tR$
 $t = r^2/2R$

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Thus, for a bright ring

$$2t = \frac{r^2}{2}$$
$$2 \ge \frac{r^2}{2R} = \frac{(2n-1)\lambda}{2}$$
$$r^2 = \frac{(2n-1)\lambda R}{2}$$

 $(2n-1)\lambda$

Replacing "r" by D/2, where "D" is Diameter

$$\frac{D^2}{4} = \frac{(2n-1)\lambda R}{2}$$
$$D_n^2 = 2\lambda R(2n-1)$$
$$D_n = \sqrt{2\lambda R(2n-1)}$$

Similarly for the Dark ring

$$2 \ge \frac{r^2}{2r} = n\lambda$$
$$r^2 = nR\lambda$$

 $2t = n\lambda$

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Replacing "r" by D/2, $\frac{D^2}{4} = nR\lambda$ $D_n^2 = 4nR\lambda$ $D_n = 2\sqrt{nR\lambda}$

Thus, the diameter of the rings is proportional to the square root of the natural numbers.

Calculating the wavelength of light:-

We have for the diameter of the nth Dark ring $D_n^2 = 4nR\lambda$

Similarly diameter for the (n+m)th Dark ring $\therefore D_{n+m}^2 - D_n^2 = 4(n+m)R\lambda - 4nR\lambda$

$$= 4nR\lambda + 4mR\lambda - 4nR\lambda$$
$$= 4mR\lambda$$
$$\therefore D_{n+m}^{2} - D_{n}^{2} = 4mR\lambda$$

$$\lambda = \frac{D_{n+m}^2 - D_n^2}{4mR}$$

How diffraction is different from interference:

Interference	Diffraction
1. It is due to superposition of two different wave fronts originating from two coherent sources.	1. It is due to superposition of secondary wavelets originating from the different parts of the same wave front.
2. Interference bands are of equal width	2.Diffraction bands decrease in their widths as the order decreases
3. All the bright fringes are of the same intensity	3. The bright fringes are of varying intensity
4. All the dark fringes have zero intensity.	4. The intensity of dark fringes is not zero

DIFFRACTION

Introduction:-

Sound waves propagate in the form of waves. Sound produces inside one room reaches other room after bending the edge of the doors (or) walls.

- The bending of waves around the abstracle is called Diffraction.
- If the light of wavelength is extremely small, there is no bending of light waves.
- If the size of the abstracle is comparable with the wavelength
- The bending of light ray around the corners of an abstracle and spreading of light ray into the geometrical shadow. This phenomenon is called Diffraction.
- The phenomenon of diffraction is divided into two types
 - 1. Fresnel's Diffraction
 - 2. Fraunhofer Diffraction

Difference between Fresnel's and Fraunhouffer Diffraction:-

Fresnel's Diffraction	Fraunhouffer Diffraction				
Either point source (or) illuminated	Extended source at infinite distance is				
narrow slit is used	used				
The wave front undergoes diffraction is	The wave front undergoes diffraction is				
either spherical (or) cylindrical	plane wave front				
The distance between the source and	The distance between the source and				
Screen is finite.	Screen is infinite.				
No lenses is used to focus the rays	Converting lenses is used to focus the rays				

Fraunhofer diffraction at single slit:



Let 'S' be a point source of monochromatic light. L_1 is the collimating lens of focal length 'f' at a distance from the source, so that the lens renders parallel rays as shown in figure. AB is the single slit of width a. the light passing through this slit is collected by lens L_2 which forms the final image on the screen MN.

Let us consider a plane wave front incident normally on the slit AB. Each and every point on the wave front will act as secondary source of light. First of all, let us consider the wave travelling along OP_0 . i.e. if we consider wave from point A, O and B, they travel straight and focus at P_0 and produce constructive interference and hence point P_0 has maximum intensity.

Now let us consider the secondary waves travelling with an angle θ to reach point P₁ on the screen. Now we have to find whether the point P₁ will have maximum or minimum intensity. To calculate this let us first draw a line perpendicular to AN from the point A. this ray is diffracted from the point B. now the distance BN gives the path difference between the secondary waves from A and N reaching point P₁.

Let us consider the

$$\Delta le \ ANB \Rightarrow \sin \theta = \frac{BN}{AB}$$

BN=AB sin θ
AB= a
 $\sim 9 \sim$

Hence the path difference = $a \sin \theta$.

Where a is the width of the slit θ is the angle of diffraction

Case (i): let us assume that this path difference is λ

Let us divide the slit AB into two halves AO and OB. The path difference between waves from point A and O reaching P_1 will be $\lambda/2$ and hence destructive interference takes place, then P_1 will be of minimum intensity.

$$a\sin\theta = \lambda$$

$$\sin\theta = \frac{\lambda}{a}$$

if θ is small, then $\sin\theta = \theta$
then $\theta = \frac{\lambda}{a}$

Case (ii): Let us assume that this path difference is 2λ

Then the slit AB has to be divided into four equal parts of width a/4 each. Then the path difference is $\lambda/4$ and hence destructive interference takes place, then P₁ will be of minimum intensity.

$$a\sin\theta = n\lambda$$

where n=1,2,3....

Case (iii): When the path difference is integral multiples of λ , minimum intensity is obtained. Then, what happens when the path difference is odd multiples of $\lambda/2$.

Let the path difference be $3\lambda/2$, i.e. between λ and 2λ . Now the slit AB of width 'a' has to be divided into equal parts of width a/3 each. Now the waves from corresponding points from first and second part will have a path difference $\lambda/2$. Hence it undergoes destructive interference. But the remaining second and third part will contribute towards intensity at point P₁. Hence P₁ will be maximum intensity. Therefore the path difference

$$a \sin \theta = (2n+1)\lambda/2$$

where n=1,2,3.... etc is the condition for secondary maxima $\sim 10 \sim$



Fig: Intensity distribution due to diffraction at single slit

Thus the diffraction pattern due to a single slit consists of a central bright maximum with secondary maxima and minima on both sides as shown in above figure.

Diffraction Grating:-

An arrangement which consists of large number of parallel slits of equal width and separating by equal space is called diffraction grating.



Let AB, CD, EF represents the slits of width "a", while BC, DE, FG represents ruling width of "b" each. Now (a+b) is the combined width and it is also the distance between the two slits. When a light ray is incident normally on a grating, the plane wave front will be acts as a secondary source of light, and then



the incident light rays will be moves in all directions, on the other side of the grating at point P_0 . P_0 is the central maxima.

The secondary diffracted waves moving in a direction which makes an angle " θ ".

A line is drawn normal to AMM'. So that image is seen at point P_1 . To calculate the central maxima,

Consider a
$$\Delta$$
le ACM
 $\Rightarrow \sin \theta = \frac{CM}{AC}$
 $\Rightarrow CM = AC \sin \theta$
 $\Rightarrow CM = (a+b) \sin \theta$

Central maxima:-

$$(a+b) \sin \theta = m\lambda \dots (1)$$
$$\Rightarrow \sin \theta = \frac{m\lambda}{(a+b)}$$
$$\Rightarrow \sin \theta = mN\lambda \dots (2)$$

Where N=
$$\frac{1}{a+b}$$
 is the number of grating elements

Grating spectrum:-

If m=1
$$\rightarrow$$
 (a+b) sin θ = m λ
(a+b) sin θ = λ
If m=2 \rightarrow (a+b) sin θ = 2 λ

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION INTERFERENCE

1. Light has ----- nature a. Particle b. Wave **Both Particle and wave** d. c. none 2. The wave nature of light is evidences a. Photo electric effect c. Blackbody radiation b. Compton effect d. Interference 3. In interference, the intensity of light gets: a. Modified b. Remains same c. A and B d. None 4. Path difference between two coherent wave is d. None a. Zero b. Constant c. A and B 5. Two light becomes interference have their amplitudes 2:1 ratio, then the intensity ratio of bright and dark fringes is: b. d. 4:1 a. 1:2 1:4 9:1 c. 6. In Newton's rings experiment the diameter of bright ring is proportional to a. $\sqrt{n-1}$ b. $\frac{(2n-1)\lambda}{2}$ c. $\sqrt{2n-1}$ \sqrt{n} d. 7. In Newton's ring experiment, the wavelength $\lambda =$ a. $\frac{D_m^2 - D_n^2}{4R(m-n)}$ b. $\frac{R(D_m^2 - D_n^2)}{4R(m-n)}$ c. $\frac{4(D_m^2 - D_n^2)}{R(m-n)}$ d. $\frac{4R(m-n)}{R(D_m^2 - D_n^2)}$ 8. Colors in soap bubbles are observed due to phenomenon of **a. Interference** b. Diffraction Polarization d. Double refraction C. 9. In young's double slit experiment, when d is the separation between the two coherent

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sources, D is the distance between the coherent sources and the screen, and λ is the wave

a. $B=\lambda d/D$ **b.** $\beta=\lambda D/d$ c. $\beta=dD/\lambda$ d. λdD 10. In constructive interference the path difference is equal to

a. $n\lambda$ b. $(2n+1)\lambda$ c. $(2n-1)\lambda$ d. $(2n+1)\lambda/2$ 11. The basis for interference of light is principle of

a. Superposition b. Newton's corpuscular theory c. Fermat d. Reflection12. To sustain the interference pattern the source must be

a. Incoherent
b. Two real
c. Highly intense
d. Coherent

13. Division of amplitude is the principle use in the study

a. Fresnel's Biprism
b. Newton's rings
c. Grating
d. Prism
14. Colors in thin films is explained using the study of

a. Polarizationb. Diffractionc. Dispersiond. Interference15. In the study of Newton's rings experiment the lens used is

a. Double concave
b. Double convex
c. Plano convex
d. Plano concave

16. Using Newton's rings experiment one can determine

a. Refractive index b. Frequency c. Speed of light D. Density

17. In Newton's rings experiment, the plane glass plate is place at this angle with the beam direction

a. 60°b. 45°c. 90°d. 30°18. With white light, Newton's rings area. Brightb. Darkc. Alternately dark and brightd. Colored

e.

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19. In interference

- a. There is loss of energy in great amount c. There is loss of energy in less amount
- **b.** There is no loss energy d. Diffraction of light

20. The path difference for thin films is given as $x=2\mu tcosr\lambda/2$. In this case interference is given by

a. Reflected lightb. Transmitted lightc. Refracted lightd. Light wave21. In the study of interference due to thin films by reflected light the central part is

a. Bright **b. Dark** c. Dull d. Colored

22. Superposition of crest and trough results into ----- interference

a. Constructive **b. Destructive** C. Damped d. Undamped

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION <u>DIFFRACTION</u>

	23. The penetration of light waves into the regions of the geometrical shadow is							
	a. interference	b. Diffraction	c.	Polarization	l	d. Reflec	ction	
	24. Diffraction phenomenon is usually divided into classes							
	a. 1	b. 2	c.	3	d.	4		
	25.The wave front under	ergoes into Fraunho	offer	diffraction is				
	a. Spherical	b. Plane	c.	Elliptical	d. C	ylindrical		
	26.In a single slit experiment if the slit width is reduced							
	a. The fringes becomes wider c. The fringes becomes harrower							
	b. No change		d.	The fringes	become	s brighter		
	27.Diffraction grating is							
a. Large number of equidistant slits c. Single slit d. Double slit						t		
	b. Large number of random distant slit							
	28. When white light is incident on a diffraction grating, the light diffracted more will be							
	a. Blue	b. Red		c. Gre	en	d. Orange		
	29.Resolving power of	a grating is						
	a. Directly prop	ortional to N		c. Directly proportional to N^2				
	b. Inversely prop	oortional to N		d. Inverse	ely prop	ortional to N ²		
	30.If 'e' is the slit with , d is distance between the slit then the condition for principle maximum in diffraction grading is:						e	
	a. (e+d) sin θ-nλ	b. (e-d) $\sin\theta = \frac{1}{2}$	nλ	c. esinθ=	dλ	d. d $\sin\theta = n$	ελ	
	31.instead of red color s	source, if blue colo	or sou	rce is used ir	n single	slit experiment		
a.	The diffraction bands becom	nes wider		c . T	he diffrac	tion pattern disappe	ears	

b.	The diffraction bands becomes narrower and crowded together a. The diffraction pattern does not change
	32. The dispersive power of a grating is
	a. $D=nN\lambda/d\lambda$ b. $n/(e+d)\sin\theta$ c. $nN/\cos\theta$ d. $nN/\sin\theta$
	33. The first diffraction grating was constructed by
	a. Newton b. Joseph von Fraunhoffer c. Einstein d. Augustin – Jean Freanel
	34. Wavelength of spectral lines can be measured using
	a. Interference b. Diffraction c. Polarization d. Diffraction Grating
	35. Diffraction grating consists of
	a. Double slit c. Large number of random distant slits
	b. Large number of equidistant slits d. Single slit
	36. In diffraction pattern due to single slit, the width of the central maximum will be
	a. Less for narrow slit c. Greater for narrow slit
	b. Less for wide slit d. Greater for wide slit
	37. The criterion of resolution of optical instruments was given by
	a. Newton b. Ransden c. Rayleigh d. Huygens
	38. Maximum number of orders available with a grating is
a.	Independent of the grating element c. Inversely proportional to the grating element
b.	Directly proportional to the grating element d. Directly proportional to the wavelength
	39. The resolving power of a grating having N slits in nth order will be
	a. (n+N) b. (n-N) c. nN d. n/N
	40. A limit on the performance of a resolving instrument is set by
	a. Interference b. Diffraction c. Polarization d. Quantum nature of light

POLARIZATION

Introduction:-

Interference and Diffraction phenomenon prove that the propagation of light is in the form of wave motion. But these phenomenon do not reveal the character of these wave motions i.e. whether it is longitudinal and transverse.

- In longitudinal waves, the particles of the medium moves to and fro in the direction of propagation of waves. Example: - Sound waves.
- In transverse waves, the particles of the medium vibrate up and down in the direction of propagation of waves Example: Ripples on a water surface

The phenomenon of polarization was discovered, that it was established that waves are transverse waves.

Unpolarized light:-

The light rays which are moving in all direction is shown as Unpolarized light.

Polarized light:-

The light which has moving only one direction is called polarized light.

Polarization:-

Polarization is the process of converting the unpolarized light into polarized light.





Propagation of Light Waves:-

Consider an ordinary beam of light is passed through a tourmaline crystal as shown in figure. The tourmaline crystal has the property of allowing the components of light that are vibrate parallel to its axis to pass through it, and it allow all the other corresponding of light that are not parallel to the axis of the crystal.

The emergent beam from the tourmaline crystal vibrates in only one direction, i.e. it vibrates parallel to the axis of the crystal. The light rays that are vibrating in only one direction are known as polarized light.

- The first tourmaline crystal that produces the polarized light is called the polarizer.
- The second tourmaline crystal is used to analyze the polarized light. Therefore, the second crystal is said to be an analyzer.



Types of Polarized light:-

There are four types of polarized light.

- 1. Plane polarized light
- 2. Partially polarized light
- 3. Circularly polarized light
- 4. Elliptically polarized light

1). Plane polarized light:-

If the vibrations are confined to a single plane i.e. either in the direction along the parallel to the plane of the paper (or) in the direction perpendicular to the

plane of the paper, then it is called Plane polarized light.



- The vibrations along parallel to the plane of the paper as shown in figure represented by arrows
- While the vibrations perpendicular to the plane of the paper are represented by dots as shown in figure.

2). partially polarized light:-

If the linearly polarized light contain small additional component of unpolarized light, it becomes partially plane polarized light. Then it is represented by either more arrows and less dots as shown in figure (a) (or) more dots as shown in figure (b).



3). circularly polarized light:-

In circularly polarization, the electric vector of constant amplitude no longer oscillates, but rotates while proceeding in the form of a helix (or) circular.

- If the vector rotates in the clockwise direction with respect to the direction of preparation, it results in right circularly polarized light.
- While the rotation in the anti-clockwise direction results in left circularly polarized light.

4). elliptically polarized light:-

If the amplitude of the electric vector is not a constant, but varies periodically, then it is elliptically polarized light.





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Double Refraction:-

Double Refraction was discovered by Bartholinus.

- When ordinary light passed through a calcite crystal, it splits into two plane polarized refracted light.
 - 1. Ordinary ray
 - 2. Extra ordinary ray
- The one which obeys laws of refraction and has vibrations perpendicular to the principle section is known as "Ordinary ray"
- The other does not obey the law of refraction and has vibrations parallel



to the principle section is called "Extra ordinary ray".

• The phenomenon is known as Double refraction.

The refractive indices of O-ray and E-ray for calcite crystal are given by

$$\mu_0 = \frac{\sin i}{\sin r_1}$$
$$\mu_e = \frac{\sin i}{\sin r_2}$$

It is clear that μ_0 is same for all the angles of incidence, while μ_e varies with angle of incidence.

- Hence O-ray travel with same velocity and it is represented by a spherical wave front.
- Whereas E-ray travel with different velocity in different directions and is given by ellipsoidal wave front.

Nicol's prism:-

Nicol's prism is one of the most important device used to produce plane polarized light. This was invented by Willum Nicol in 1828.

A calcite crystal whose length is three times breath is taken. The two ends AB and CD of the crystal are cut, so that the angles ABC reduces from 71° to



68° as shown in figure. Then the crystal is cut into two halves along the plane AC, which passes through the blunt corners and perpendicular to both the principle section and end faces. A₁C₁ makes an angle of 90° with C₁Dand A₁B. The two cut faces are well polished and cemented together using a thin layer of Canada balsam, a clear transparent material has refractive index 1.55 for λ =5893 A°.

When unpolarized light enters the Nicol prism, it splits into O-ray and E-ray.

- O-ray has the refractive index 1.6584, while the e-ray has the refractive index varies from 1.4864 to 1.6584.
- Inside the crystal when O-ray meets the thin layer of Canada balsam, it has to travel from denser medium to rarer medium.
- Because of shaping of the crystal face, the O-ray is refracted more so that the angle of incidence at the Canada balsam interface is greater than the critical angle.
- Hence it undergoes total internal reflection as shown in figure. Hence E-ray alone emerges out of the other face of the prism.
- Nicol prism is good polarizer and analyzer and can be used to produce and analyze the plane polarized light.

Quarter Wave Plate:-

A quarter wave plate (QWP) is a device from a doubly refracting uniaxial crystal, whose refracting faces are cut parallel to the direction of the optic axis as shown in figure. When plane polarized light is incident on calcite crystal, the light splits up into O-ray and E-ray. As a result, a phase difference is introduced between them.

Let μ_e and μ_o be the refractive indices of the extraordinary and ordinary rays respectively. Let "t" be the thickness of the crystal.

Optical path of O-ray = $\mu_0 t$

Optical path of E-ray = $\mu_e t$

Hence Optical path difference = $\mu_0 t - \mu_e t = (\mu_0 - \mu_e)t$



Then for a negative crystal ($\mu_0 > \mu_e$), then the path difference between these two rays is ($\mu_0 - \mu_e$)t

The QWP is cut in such a way that it can produce a path difference of $\lambda/4$.

i.e.
$$(\mu_0 - \mu_e) t = \frac{\lambda}{4}$$

 $t = \frac{\lambda}{4(\mu_0 - \mu_e)}$

Then for a positive crystal ($\mu_e > \mu_0$), path difference between the ordinary and extra ordinary rays is (μ_e - μ_0) t.

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The thickness of a QWP made up of positive crystal can be obtained by equating their path difference to $\lambda/4$.

i.e.
$$(\mu_{e} - \mu_{0}) t = \frac{\lambda}{4}$$

$$t = \frac{\lambda}{4 (\mu_{e} - \mu_{0})}$$

Half Wave Plate:-

A half wave plate (HWP) is a doubly refracting uniaxial negative (or) positive crystal cur in such a way that it can produce a phase difference of " π " (or) path difference of " $\lambda/2$ " between the ordinary and extra ordinary rays.

Let μ_e and μ_o be the refractive indices of the extraordinary and ordinary rays respectively. Let "t" be the thickness of the crystal.

Optical path of O-ray = $\mu_0 t$ Optical path of E-ray = $\mu_e t$

Hence Optical path difference = $\mu_0 t - \mu_e t = (\mu_0 - \mu_e)t$

Then for a negative crystal ($\mu_0 > \mu_e$), then the path difference between these two rays is (μ_0 - μ_e)t

The HWP is cut in such a way that it can produce a path difference of $\lambda/2$.

i.e.
$$(\mu_0 - \mu_e) t = \frac{\lambda}{2}$$

 $\Rightarrow t = \frac{\lambda}{2(\mu_0 - \mu_e)}$

Then for a positive crystal ($\mu_e > \mu_0$), path difference between the ordinary and extra ordinary rays is (μ_e - μ_0) t.

The thickness of a HWP made up of positive crystal can be obtained by equating their path difference to $\lambda/2$.

i.e.
$$(\mu_{\rm e} - \mu_0) t = \frac{\lambda}{2}$$

 $\Rightarrow t = \frac{\lambda}{2 (\mu_{\rm e} - \mu_0)}$

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION <u>POLARAISATION</u>

41.Polarization of light is evidence for

;	a. T	ransverse nat	ure of light	c. Quantur	n nature of light			
1	b. L	ongitudinal na	ture of light	d. Corpuse	cular nature of lig	ght		
42.N	42.Nicol prism is based on the principle of							
i	a. R	etraction	b. Double refract	tion c	. Reflection	d. Scattering		
43.7	The C	-ray obeys						
		a. Snell's La	IW		c. Brewster L	aw		
		b. Does not c	bbey Snell's Law		d. Does not ol	bey Brewster Law		
44.I	n do	ble refraction						
a	a. The velocity of ordinary ray is same in all direction							
b	. The	velocity of ex	xtra ordinary ray is s	ame in all di	irections			
с	. Bot	h a and b						
d	. Firs	t o-ray have h	igh velocity, finally	e-ray have h	nigh velocity			
45.I	n sou	ind, following	phenomenon does n	ot takes pla	ce			
		a. Interference	ce b. Polarizat	ion c.	Diffraction	d. Scattering		
46.7	The e	xamples for ne	egative crystal					
		a. calcite	b. Ice	c.	Quartz	d. Water		
47.On rotating the analyzer, the intensity of emergent light varies between a maximum and minimum which is zero, then the light incident m the analyzer is								
a. U	Jnpo	larized b. Ci	rcularly polarized	c. Elliptica	ally polarized	d. Plane polarized		
48. <i>A</i> tl	48.An axis of two nicol prisms is parallel to one another. One of two nicols is rotated through an angle of 60. The rotation of the intensity of transmitted light before and after rotation is							

	a. 1:2	b. 2:1	c. 1:4	d. 4:1
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49.In elliptically polarized light

- a. Amplitude of vibrations changes in direction only
- b. Amplitude of vibrations changes in magnitude only

c. Amplitude of vibrations changes in magnitude and direction

- d. Amplitude of vibrations does not changes in magnitude and direction
- 50. A glass slab has the angles of polarization 62°24', then the refractive index of the glass slab is
 - a. **1.91** b. 19.1 c. 0.191 d. 191
- 51. The light waves are transverse in nature establish beyond doubt by
- a. Fresnel's diffraction
 b. Fraunhoffer diffraction
 c. Polarization
 d. Interference

 52. The plane of polarization is that plane in which
 - a. Few vibrations occurb. Number of vibrations occursc. No vibrations occurd. Mixed vibrations occur
- 53. The plane of vibration is that plane in which
- a. Vibrations occur at right angles to the plane of polarization
 b. Few vibrations occur
 c. No vibrations occur
 d. Mixed vibrations occur
 - 54. The angle of polarization is related to
 - a. Brewster's Law b. Snell's Law c. Newton's Law d. Braggs Law
 - 55. When a monochromatic light is passed through nicol prism, it splits in two rays, one ray through the nicol prism is
 - a. Ordinary ray b. **Extra ordinary ray** c. Scattered ray d. Reflected ray
 - 56. The plane polarized light can be produced by using
 - a. Rochon Prism b. Wallaston prism c. Nicol Prism d. Some other prism

- 57. The refractive index of Canada Balsam is
 - a. Greater than ordinary ray
 - b. Less than extra ordinary ray
 - c. Equal to the ordinary ray

d. Lies between ordinary and extraordinary ray

- 58. The phenomenon by which splitting of light into e-ray and o-ray is known as
 - a. Refraction b. Selective absorption c. Double refraction d. Scattering
- 59. A birefringent crystal has refractive indices μ_o and μ_e for the rays. If the crystal is to function as a quarter wave plate, the number of wavelengths, each component as the waves travel within the crystal thickness must differ by
 - a. 4 b. $\lambda/4$ c. λ d. $\lambda/2$
- 60. A half wave plate introduces ------ phase difference between the ordinary and extraordinary rays
 - a. 0 b. $\pi/2$ c. π d. 2π
Problems on Interference

 Newton's rings are observed in the reflected light of wavelength 5900A°. The diameter of 10th dark ring is 0.5 cm. find the radius of curvature of lens used. Sol: Given that

> The wavelength of reflected light λ =5900A°=5900x10⁻¹⁰m The diameter of 10th dark ring D10=0.5cm=0.0005 m=5x10⁻³ m. The expression for the diameter of nth dark ring

$$R = \frac{D_n^2}{4n\lambda} = \frac{\left(5x10^{-3}\right)^2}{4x10x5900x10^{-10}} = 1.059m$$

The radius of curvature of the lens R=1.059 m.

2. In Newton's rings experiment the diameter of 15th ring was found to be 0.59 cm and that of 5th ring 0.336 cm. the radius of curvature of the lens is 100 cm. Find the wavelength of light.

Sol: Given that

The diameter of 15^{th} ring, $D_{15}=0.59 \text{ cm} = 5.9 \times 10^{-3} \text{ m}$ The diameter of 5^{th} ring, $D_5=0.336 \text{ cm}=3.36 \times 10^{-3} \text{ m}$ The radius of curvature of lens R=100cm=1 m The expression for wavelength of light is

$$\lambda = \frac{D_{n+m}^2 - D_n^2}{4mR}$$

Here (n + p) = 15 and n = 5, therefore

$$\lambda = \frac{D_{15}^2 - D^2 5}{4x10xR} = \frac{(5.9x10 - 3)^2 - (3.36x10 - 3)^2}{4x10x1} = 0.588x10^{-6}m = 588 \text{ nm}$$

The wavelength of the light λ =588 nm

3. In Newton's rings experiment the diameter of 8th ring was found to be 0.35 cm and that of 18th ring 0.65 cm. if the wavelength of the light 6000A° is used than find the radius of curvature of the plano-convex lens.

Sol: Given that

The diameter of the 8th ring D₈=0.35 cm The diameter of the 18th ring, D₁₈=0.65 cm The wavelength of the light, λ =6000A°=6000x10⁻⁸ cm. The expression for wavelength of light $\lambda = \frac{D_{n+m}^2 - D_n^2}{\Delta m R}$

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$$R = \frac{D_{n+m}^2 - D_n^2}{4m\lambda} = \frac{D_{18}^2 - D_8^2}{4x10x\lambda}$$
$$R = \frac{(0.65)^2 - (0.352)^2}{4x10x6000x10^{-8}} = 125cm$$

The radius of curvature of the lens R=125 cm=1.25 m.

4. Calculate the thickness of the air film at 10th dark ring in Newton's rings system viewed normally by a reflected light of wavelength 500 nm. The diameter of 10th dark ring is 2 mm.

Sol: Given that

The wavelength of reflected light λ =500 nm = 500x10⁻⁹ m The diameter of 10th dark ring D₁₀=2 mm=2x10⁻³ m The expression for diameter of dark ring

$$D_n^2 = 4n\lambda R$$

$$\therefore R = \frac{D_n^2}{4n\lambda} = \frac{(2x10^{-3})^2}{4x10x500x10^{-9}} = 0.2m$$

The radius of curvature of the convex lens R=0.2 m The expression for the thickness of air film at nth dark ring is

$$2t = \frac{D_n^2}{4R}$$

$$t = \frac{D_n^2}{8R}$$

If $n = 10$, then $t = \frac{(2x10^{-3})^2}{8x0.2} = 2.5x10^{-6}m = 2.5\mu m$

Problems on Diffraction

5. A plane transmission grating having 4250 lines per cm is illuminated with sodium light normally. In second order spectrum the spectral lines deviated by 30° are observed. Find the wavelength of the spectral line.

Sol: Given that

The number of lines per cm on grating N=4250 The angle of diffraction θ =30° Order of the spectrum n=2 We know that $\lambda = \frac{\sin \theta}{\sin \theta} = \frac{\sin 30}{2} = \frac{0.5}{2} = 5.882 \times 10^{-5} \text{ cm} = 58$

We know that
$$\lambda = \frac{\sin \theta}{Nn} = \frac{\sin \theta}{4250x2} = \frac{0.3}{8500} = 5.882x10^{-5}cm = 5882A^{\circ}$$

The wavelength of the spectral line λ =5882 A°

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Problems on Polaraisation

Calculate the thickness of a mica sheet required for making a quarter wave plate for λ=5460A°. The indices of refraction for the ordinary and extraordinary rays in mica are 1.586 and 1.592.

Sol: Given that,

The wavelength of light λ =5460A°=5460x10⁻¹⁰ m The refractive index of mica for ordinary ray μ_0 =1.586 The refractive index of mica for extraordinary ray μ_e =1.586 We know that the thickness of a quarter wave plate is

$$t = \frac{\lambda}{4(\mu_e - \mu_o)}$$
$$t = \frac{5460 \times 10^{-10}}{4(1.592 - 1.586)} = 2.275 \times 10^{-5} m = 22.75 \,\mu m$$

The thickness of quarter wave plate t= $22.75 \ \mu m$

7. Calculate the thickness of a quarter wave plate for light of wavelength 6000A°. $(\mu_e=1.554, \mu_0=1.544)$

Sol: Given that,

The wavelength of light λ =6000A°=6000x10⁻¹⁰ m The refractive index of mica for ordinary ray μ_0 =1.554 The refractive index of mica for extraordinary ray μ_e =1.544 We know that the thickness of a quarter wave plate is

$$t = \frac{6000 \times 10^{-10}}{4(1.554 - 1.544)} = 1.5 \times 10^{-5} m^{-5} t = \frac{\lambda}{4(\mu_0 - \mu_e)}$$

The thickness of quarter wave plate $t = 1.5 \times 10^{-5} \text{m}$

8. Calculate the thickness of half wave plate of quartz for a wavelength 500 nm. Here $(\mu_e=1.553, \mu_0=1.544)$

Sol: Given that

The wavelength of light λ =500 nm=500 x10⁻⁹ m The refractive index of mica for ordinary ray μ_0 =1.553 The refractive index of mica for extraordinary ray μ_e =1.544 We know that the thickness of a quarter wave plate is

$$t = \frac{\lambda}{2(\mu_0 - \mu_e)}$$
$$t = \frac{500 \times 10^{-9}}{2(1.553 - 1.544)} = 2.777 \times 10^{-5} m = 27.77 \,\mu m$$

<u>UNIT – II</u>

Chapter – I: LASERS

Chapter – II: Fiber optics

Course Outcome:

CO 2: Analyse and understand various types of lasers & optical fibers. (K4)

<u>APPLIED PHYSICS</u> <u>UNIT-II</u>

LASER

Introduction:-

The word "Laser" stands for "Light Amplification by Stimulated Emission of Radiation"

- Laser is outcome of "MASER". It stands for "Microwave amplification and Stimulated Emission of Radiation".
- Laser Principle is extended up to X-Rays and Gamma rays. Gamma ray lasers are called "GASERS"
- Laser are used many fields of Science and technology like radio astronomy, satellite communication, optical fiber communication, holography, data processing, testing and welding of materials, medicine etc.

Characteristics of Lasers:-

Laser differs from conventional light source in a number of ways such as sun, a flame or incandescent lamps. The most striking features of laser beam are

- 1. High Directional
- 2. High Intensity
- 3. High Monochomaticity
- 4. High Degree of Coherence

High Directionality:-

The conventional light sources emit light in all directions due to spontaneous emission. On the other hand, laser emits light only in one direction due to stimulated emission. The directionality of the laser beam is also expressed in terms of divergence. The divergence $\Delta \theta = \frac{r_2 - r_1}{d_2 - d_1}$,

Where r_1 and r_2 are the radai of laser beam spots at distance d_1 and d_2 respectively.

High Intensity:-

The laser gives out light into a narrow beam and its energy is concentrated in a small region and has a great intensity.

Ex: 1 Watt of laser would appear many thousand times more intense than 100 watt of ordinary lamp.

So, laser light is intense light, because of all the emitted waves are in phase or coherent. In coherent beam, the resultant intensity is the sum of individual intensities and is proportional to na^2

Where 'n' is the number of waves 'a' is the amplitude of each wave

High Monochomaticity:-

Laser light is a monochromatic light, because all the photons have the same energy (E_2-E_1) above the ground state and they have the same frequency.

i.e
$$hv = E_2 - E_1$$

 $v = E_2 - E_1 / h$

The laser source is the best monochromatic source.

High Degree of Coherence:-

The laser has a high degree of coherence, because all the photons or waves are in phase. That is, purity of the spectral line is expressed in terms of coherence. Due to its coherence only, it is possible to create high power in space with laser beam.

Fundamental terms of lasers:-

- 1. Absorption
- 2. Spontaneous emission
- 3. Stimulated emission
- 4. Population Inversion

Absorption:-

The process of moving electron from ground state to excited state with the supply of energy is known as "Absorption".

(Or)

An atom (or) molecules in the ground state E_1 can absorb a photon of energy hv and go to the excited state E_2 . This process is known as "Absorption"



Rate of Absorption = $B_{12} \rho$ (v) N_1

Where B_{12} - Einstein coefficient of absorption

N1 - Concentration of electron in ground state

 $\rho(v)$ – Energy density

Spontaneous emission:-

The emission of electron from excited state to the ground state on their own without any supply of external energy is known as "Spontaneous emission".

The excited atom does not remain in that state for a long time. After a short interval of time i.e. 10^{-8} sec, it falls to its ground state by emitting a photon as shown in figure.



Here the excited atoms jumps back to its ground state on its own and hence the process is called Spontaneous emission

i.e.	Rate of Spontaneous emission = $A_{21}N_2$
Where	A ₂₁ - Einstein coefficient of absorption
	N ₂ - Concentration of electron in excited state

Stimulated emission:-

The emission of electron from the excited state to ground state with the supply of external energy is known as stimulated emission.

The process of speeding up the atomic transition from the excited state to ground state is called Stimulated emission.



Rate of Stimulated emission = $B_{21} \rho$ (v) N_2

Where B_{21} - Einstein coefficient of absorption N₂ - Concentration of electron in excited state $\rho(v)$ – Energy density

Difference between Spontaneous emission Stimulated emissions:-

Spontaneous emission	Stimulated emissions			
The emission of electron moving on	The emission of electron from the			
their own from excited state to ground	excited state to ground state with the			
state is known as Spontaneous emission	supply of external energy is known as			
	stimulated emission.			
It is non- directional	It is highly directional			
Spontaneous emission is in-coherent	Stimulated emissions is coherent			
Intensity of laser radiation is low.	Intensity of laser radiation is high.			
Spontaneous emission cannot be	Stimulated emissions can be controlled			
controlled from outside	from outside			
sodium lamp and mercury lamp are the	Ruby laser and He-Ne gas lasers are the			
examples of Spontaneous emission	examples of Stimulated emissions			

Population Inversion:-

Finding more number of electrons in higher energy level than lower energy level is known as population inversion.



Population inversion is a pre required condition in order to have laser radiation. This population inversion can be understood in terms of metastable energy level.



Metastable State:-

The energy level which exits in between ground state energy level and excited energy level is known as metastable energy level.

Metastable state is a particular excited state of an atom that has longer life time the ordinary excited states. A than metastable state is an intermediate state. The



life time of an atom in the metastable state is 10^{-3} sec.

Pumping:

Pumping is the process of supplying energy. The pump is an external source that supplies energy needed to transfer atoms from lower energy level to upper energy level. There are a number of techniques for pumping. Optical pumping and electric discharge are some of the methods. In optical pumping a light source is used and in electric discharge method an electric field is used to transfer atoms from lower energy level to upper energy level.

Life Time:

The amount of time in which an atom stays in an energy state is called life time. The life time of an atom in the ground state is unlimited but it is 10⁻⁸ sec in the excited state.

Types of Lasers:-

Lasers are of different types basing on types basing on the type of active medium that we have with the Laser. Some of the important lasers are

- 1. Solid state laser Ruby laser
- 2. Gas laser He-Ne gas laser

Ruby Laser:-

The Ruby Laser namely called as "solid state laser". This is being constructed in the year 1961 by T.H. Maiman.

Ruby laser has the laser output to be in visible region. i.e. the output of ruby laser is red in color. Ruby laser finds good number of applications in so many fields like atmospheric sciences, engineering medicine and the technology.

Construction of Laser:-

Ruby laser can be identified by means of three important parts of it.

- 1. Energy source Xenon flash tube
- 2. Active medium Ruby rod
- 3. Active centers $-Cr^{3+}$ ions.
- 4. Reflecting mirrors Polished opposite ends

Description:-

A ruby laser consists of ruby rod prepared out of Al_2O_3 with 0.05% of Cr_2O_3 . Cr^{3+} ions will act as active centers. The ruby rod appears pink in color due to presence of Cr^{3+} ions. The ends face of the rod is highly polished and then silvered while the other end partially reflecting. The ruby rod is



enclosed in a glass tube and surrounded by xenon flash lamp, which provides the pumping light to raise the ions to upper energy level. The flash tube not only emits light but also emits heat, so a cooling system is used.

Working Principle:-

Almost all atoms are initially in ground state. When the energy is applied by a xenon flash lamp, which emits a radiation of 5600A°. The atoms move to an upper energy level by absorbing light photons of wavelength. It will absorb the energy at two specific wavelengths. i.e. blue, green. Upon absorption of energy the Cr^{3+} ions will go excited to the energy level E_2 and E_3 respectively. The ruby laser we came across two prominent transitions $E_2 \rightarrow E_3$, $E_3 \rightarrow E_1$.

Energy level Diagram:-

Ruby laser is a three level energy laser. i.e. it consists of three energy levels.

i.e.
$$E_1(G.S), E_2(E.S), E_3(M.S)$$

Now the excited atoms can return in to two steps. The first transition from E_2 - E_3 (Metastable state). Which is a shorter jump and energy emitted in this transition is not radiated in the form of photons and this transition is called "Non radiative transition" or "Radiation less transition". The Cr³⁺ atoms return to E_3 level can remain in this state atom long time. The accumulation of



atoms in E_3 level increases the population at E_3 level. After a short interval of time population inversion is created between E_3 and E_1 .

From E_3 to E_1 by the process of stimulated emission a high intense light of wavelength 6943A° is emitted. i.e. a laser produced in visible region.

Merits:-

- 1. The output of ruby laser falls in visible region
- 2. It can cause output only in one color (red)
- 3. The laser radiation is not harmful.

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Demerits:-

- 1. Ruby laser cannot produce continuous beams of lasers
- 2. The output of this laser is discontinuous
- 3. Intensity of laser radiation is very less
- 4. Unnecessary heat will generated at active medium
- 5. Separate cooling arrangement is required

Gas Lasers (Helium – Neon Laser):-

He - Ne gas laser was first gas laser constructed in the year 1961, by scientist "Alijavan". This laser can cause continuous laser beam . He - Ne gas laser finds good number of application.



Description:-

He – Ne gas laser consists of long narrow quartz tube of 80cm length and 1.5cm in diameter. This will get filled with He – Ne gas laser mixture taken in the ratio 10:1 with a pressure of about 1mm of mercury. Both ends of the tube are silvered. One of them is partially silvered, so that sufficiently built laser beam passes through it. A high frequency electric discharge, acts as a pumping source, to excite the He – Ne mixture. The reflecting mirrors are arranged at the opposite ends of the quartz tube.

Working Principle:-

When electric discharge is passed through the He – Ne mixture, electrons from the discharge source collide with He – Ne atoms and thus transfer of their energy to these atoms. As a result He – Ne atoms are excited to higher state He_2 and He_3 in case of helium and Ne_4 and Ne_6 in case of neon. These are their metastable states.



The atoms remain in these levels for a sufficiently longer time. After their life time He atoms collide with Ne atoms, which are in the ground state, while the He atoms return to their metastable states. As the energy exchange continuous, the population of Ne atoms, in the excited states increases more and more and population inversion takes place.

Thus by the process of stimulated emission between Ne_6 and Ne_3 laser light is emitted with a wavelength of 6328A°. The Ne atoms are returned to the ground state by non-radiative transition. After arriving ground state once again the Ne atoms are excited to higher state by the collisions of the atoms. This process continuous and continuous laser beam is produced.

Merits:-

- 1. No exchange heat can develop
- 2. We require no separate cooling arrangement
- 3. The output result will last for long time.

Applications of Laser:-

Laser finds wide and variety of applications in various fields basing on Directionality, Intensity, Monochomaticity and Coherence.

The applications of laser are wide spread over various scientific disciplines such as physics, chemistry, biology, medicine etc. They have exciting potential applications in industry, communication and warfare.

Lasers in Medicine:-

- 1. Laser radiation is often used in controlling hemorrhages.
- 2. Lasers are used in destroying kidney stones.
- 3. Lasers are used in ophthalmology to reattach a detached Retina.
- 4. They are used in cancer diagnosis and therapy and also stomotology.

Lasers in Industry/Engineering:-

- 1. They are used to blost holes in diamond and hard steel.
- 2. Lasers are used to test quality of a fabric.
- 3. It has been observed that finger prints on documents, current bills, cloths etc.
- 4. Laser cutting technology is widely used in the fabrication of Spacecrafts.

Lasers in Science and Research:-

- 1. Lasers are best suited for optical communication.
- 2. Lasers are used to study the internal structure of micro organisms and cells.
- 3. Lasers are used for isotopic separation.
- 4. Lasers are used to produce certain chemical reactions.
- 5. Lasers have several applications in the field of computers.
- 6. To transmit memory blanks from one computer to another.
- 7. Laser is used in computer printers.
- 8. It is used to read the data from CD-ROM.

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

1.	Emission of photon when an electron jumps higher energy state to lower energy state due to interaction of external energy is called					
a.	Spontaneous emission	c. Induced absorption	on			
b.	Stimulated emission	d. Amplified emissi	on			
2.	The population of the various e equilibrium is given by	nergy level of a system in	thermal			
	a. Boltzmann distribution lav	w c. Plank's law				
	b. Einstein relation	d. Beer's law				
3.	The color of the laser output from	om a ruby laser is				
	a. Green b. Blue	c. Red	d. Violet			
4.	In Ruby lasing material the per- is	centage of chromium ions	in aluminum oxide			
	a. 0.5 b. 0.05	c. 5	d. 0.005			
5.	In He-Ne laser, the ratio of He-	Ne is in the order				
	a. 1:10 b. 1:1	c. 100 : 1	d. 10:1			
6.	The wavelength of emission from	om He-Ne laser is				
	a. 10.64µm b. 337.1nm	c. 794.3nm	d. 632.8 nm			
7.	Laser radiation is					
	a. Monochromatic	c. Coherent and stimu	lated			
	b. Highly directional	d. Highly directional coherent and stime	, monochromatic, ılated			
8.	He-Ne gas laser is					
	a. Pulsed laser	c. Solid state lase	er			
	b. Semiconductor laser	d. Continuous la	aser			

9. The lasing act	9. The lasing action is possible only if there is					
a. A set of ref	lecting mirrors	c. Population in	version			
b. A black bo	dy	d. Incandescent l	amp			
10.The pumping	process used in Ruby la	aser is				
a. Optical pu	mping	c. Atom – atom i	in elastic collision			
b. Electric dis	charge	d. Chemical reac	tion			
11. In He-Ne lase	r, atoms involved in las	ser emission are				
a. Ne-atoms	b. He-atoms	c. Both	d. none			
12. Rate of stimu	lated emission is propor	rtional to				
a. Brightness	b. Monochromaticity	c. Directionality	d. Coherence			
13. Emission of p energy state du	13. Emission of photon when an electron jumps higher energy state to lower energy state due to interaction with another photon is called					
a. Spontaneous e	mission	c. Induced abs	orption			
b. Stimulated en	nission	d. Amplified e	mission			
14. Ruby laser is	the best example for a -	level syster	n			
a. Two	b. Three	c. Four	d. single			
15. He- Ne laser i	s a level laser	system				
a. Two	b. Three	c. Four	d. Single			
16. Important cha	racteristics of laser bea	ım is				
a. Interference	b. Diffraction	c. Dispersion	d. coherence			
17. Supply of ene	rgy to atoms for excitat	tion is called				
a. Glowing	b. bombarding	c. incidenting	d. Pumping			
18. The lifetime of	of an atom in a metastab	ble state is of the ord	er of			
a. Few seconds	b. Unlimited time	c. Electric discha	rge d. None			

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- 19. The emission of photons without being aided by any external agency is called
 - a. Light amplification c. Stimulated emission
 - b. Induced absorption d. Spontaneous emission
- 20. The rate of stimulated emission is equal to
- a. $B_{12} \rho(v) N_1$ b. $B_{21} \rho(v) N_2$ c. $B_{12} \rho(v) N_2$ d. $B_{21} \rho(v) N_1$

FIBER OPTICS

Introduction:

Fiber optics is the branch of physics, which deals with the transmission of light rays using optical fibers.

Optical Fiber:-

An optical fiber is a dielectric wave guide, which having high tensile strength, which will be capable to transmitting the signals with no loss of energy.

(Or)

Optical Fibers are wave guide inside which light signals can travel.

- Optical Fiber causes the communication basing on the principal of "Total Internal Reflection (TIR)"
- The optical fiber communication is being realized in terms of simple observations of "Sir John Tyndoll" in the year 1857.
- According to these observations light rays can be made to pass through narrow streams of water coming out of small opening by "Total Internal Reflection (TIR)"



- The optical fiber are being first utilized in the year 1927 in U.S.A, for transmission of voice signals and it has began from 1957.
- Laser along with optical fibers have brought in so much of unprecedencial development in the field of communication.

Structure of optical fiber:-

Optical Fiber is a very thin, narrow and flexible wire having a cylinder shape consisting of three parts or sections.

- 1. Core
- 2. Cladding
- 3. Buffer (or) Sheath (or) Outer Jacket.

The structure of optical fiber is a shown in below figure



Core and cladding:-

The core is central part of optical fiber to facilitate the "Total Internal Reflection (TIR)". The core is made up of pure silica (SiO₂) glass and its diameter is ~50 μ m, which is surrounded by a cladding whose diameter is ~125 μ m. The cladding is formed by the addition of small amounts of boron, germanium (or) phosphorus in SiO₂ glass to increase the refractive index of the core than cladding to satisfy the condition of Total Internal Reflection.

Sheath:-

To protect the fiber material and also give mechanical support, there is a protective cover called the Outer Jacket. It is made up of plastic material. In order to avoid damages it acts as a protective cover.

The optical fiber will get basically prepared in terms of either the glass (or) plastic material, depending on the way that we prepare the optical fiber. Optical fiber can broadly into 3 types, they are

- 1. Glass Glass Fiber
- 2. Glass Plastic Fiber
- 3. Plastic Plastic Fiber

Principal of Optical Fiber: - (Total Internal Reflection)

The light travels through optical fiber on the principle of "Total Internal Reflection"

The Total Internal Reflection takes place only when the following two conditions are satisfied.

- 1. The refractive index of the core (n_1) must be greater than that of the cladding (n_2) .
- 2. The angle of incidence (θ) must be greater than the critical angle (θ_c).



When light ray travels from core of refractive index n_1 to the cladding of refractive index n_2 , refraction occurs. Since light travels from denser to rarer medium, the angle of refraction is greater than the angle of incidence, which is shown in figure (a).

With the increase in angle of incidence, the angle of refraction also increases, and for a particular angle of incidence ($\theta=\theta_c$) the refracted ray simply pass through the interface between the core and cladding. That angle we called it an incidence angle, which is shown in figure (b).

When the angle of incidence is further increased the ray is reflected back into the core. This phenomenon is called "Total Internal Reflection"

According to law of refraction $n_1 \sin \theta_1 = n_2 \sin \theta_2$ (1) When $\theta_1 = \theta_c$ $\theta_2 = 90^\circ$ Therefore $n_1 \sin \theta_c = n_2 \sin 90$ $\sim 17 \sim$

$$\therefore \sin \theta_{c} = \frac{n_{2}}{n_{1}} \dots \dots (2)$$
$$\theta_{c} = \sin^{-1} \left(\frac{n_{2}}{n_{1}} \right) \dots \dots (3)$$

From equation (3) is the condition for "Total Internal Reflection"

"The reflection of light rays into the same medium, when the light rays are made to pass from denser medium to rarer medium with an angle of incidence greater than the critical angle is known as "Total Internal Reflection".

Acceptance angle:-

When a light beam launched into a fiber at its one end, the entire light may not pass through the core, only the rays make the angle of incidence greater than the critical angle at the core, cladding interface



undergo "Total Internal Reflection" and propagate through core. The other rays are refracted into the cladding material and are lost. Hence it is essential to know at what angle known as "Acceptance angle". We have launched the beam at its end to enable the entire light to propagate through the core.

The light is launched form a medium (air) of refractive index n_0 (`1) into core of refractive index n_1 . The ray enters with an angle of incidence α_i to the fiber end face at a point "A" and proceeds after refraction at an angle α_r . Then it undergoes total internal reflection at "B" on core wall at an angle of incidence " θ ".

According to Snell's law, we have $\frac{Sin \ \alpha_i}{Sin \ \alpha_r} = \frac{n_1}{n_0} \quad \dots \dots \dots (1)$ $Sin \ \alpha_i = \frac{n_1}{n_0} \quad Sin \ \alpha_r$ From Δ le ABC $\Rightarrow \ \alpha_r = (90-\theta)$

 α_i be the maximum possible angle of incidence at "A", when $\theta=\theta_c$ The equation (2) can be written as

$$\therefore \sin \alpha_i(\max) = \frac{n_1}{n_0} \cos \theta_c \quad \dots \dots \quad (3)$$

$$\therefore \cos \theta_c = \sqrt{1 - \sin^2 \theta_c}$$

$$= \sqrt{1 - \frac{n_2^2}{n_1^2}} \quad \because \sin \theta_c = \frac{n_2}{n_1}$$

$$= \sqrt{\frac{n_1^2 - n_2^2}{n_1^2}} \quad \dots \dots \quad (4)$$

Substitute equation (4) in equation (3)

$$\sin \alpha_{i}(\max) = \frac{n_{1}}{n_{0}} \sqrt{\frac{n_{1}^{2} - n_{2}^{2}}{n_{1}^{2}}}$$

$$= \frac{n_{1}}{n_{0}} \frac{\sqrt{n_{1}^{2} - n_{2}^{2}}}{n_{1}}$$

$$= \frac{\sqrt{n_{1}^{2} - n_{2}^{2}}}{n_{0}}$$

! Here n_0 is refractive index of air $(n_0) = 1$.

$$\sin \alpha_{i}(\max) = \sqrt{n_{1}^{2} - n_{2}^{2}}$$

 $\alpha_{i}(\max) = \sin - 1 \left(\sqrt{n_{1}^{2} - n_{2}^{2}}\right)$

Thus "maximum angle α_i is called "acceptance angle".

Acceptance Cone:-

Rotating the acceptance angle about the fiber axis describes the acceptance cone of the fiber. Half angle is called acceptance cone.



Numerical Aperture (NA):-

Light collecting capacity o the fiber is expressed in terms of Numerical aperture (Or)

Light gathering ability of an optical fiber in order to propagate through it is known as "Numerical Aperture" (Or)

Sine of maximum acceptance angle is known as "Numerical Aperture"

i.e. Numerical Aperture = $\sin \alpha_i(\max) = \sqrt{n_1^2 - n_2^2}$ (1)

Let
$$\Delta = \frac{n_1^2 \cdot n_2^2}{2n_1^2}$$
(2)
 $\therefore n_1^2 \cdot n_2^2 = 2n_1^2 \Delta$
 $\sqrt{n_1^2 \cdot n_2^2} = n_1 \sqrt{2\Delta}$ (3)

Substituting equation (3) in eq (1)

$$NA = n_1 \sqrt{2\Delta}$$

 Δ is the fractional difference between the refractive indices of the core and cladding known as fractional refractive index change.

The Numerical Aperture of the fiber is effectively depends on the refractive indices of core and cladding material, but not on the fiber dimensions. The value of numerical aperture ranges from 0.13 to 0.50.

Advantages of optical fiber in communication system:-

- 1. Extremely wide band width, the rate at which information can be transmitted is directly related tp signals frequency. Light has very high frequency in the range 1014 to 1015 Hz. So, the optical signal can transmit information at a higher rate.
- 2. Smaller diameter, light weight cables.
- 3. Lack of cross talk between parallel fibers.
- 4. Potential of delivering signals at low cost
- 5. Much safer than copper cables.
- 6. Longer life span
- 7. High temperature resistance.
- 8. Optical fibers are more reliable and easy to maintain than copper cables.

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

21. In an optical fiber, if n_1 is the refractive index of core and n_2 is the reflective index of cladding. Then

e.
$$\frac{n_1 - n_2}{n_1} < 1$$
 f. $\frac{n_1 - n_2}{n_1} > 1$

- 22. Choose the correct statement
- a. Cladding has higher refractive index than core
- c. Cladding is for providing mechanical strength to the fiber

- b. Core has higher refractive index than cladding
- d. The loss in wave guides without cladding is very low
- 23.In the case of an optical fiber the acceptance angle equal to
- a. $Sin^{-1}(n_1^2 n_2^2)^{1/2}$ b. $Sin^{-1}(n_1^2 n_2^2)$ c. $Sin^{-1}(n_1 n_2)$ d. $Sin^{-1}(n_1 n_2)^{1/2}$
- 24. Total internal reflection takes place when light travels from

a. Denser to rarer medium b. Any medium to other different medium c. Air to liquid or solid d. A lighter to denser medium 25. The refractive index of core and cladding are 1.563 and 1.498 respectively then Numerical Aperture (NA) is a. 0.446 b. 0.246 c. 0.1999 d. 0.346 26. If the angle of incidence of ray is greater than the critical angle at the interface of core and cladding then the ray travels

- a. In the core b. In the cladding c. Along the d. In buffer interface
- 27. To enter an optical signals into the core the angle of incidence at the interface of air and core should be
- a. Equal to critical angle c. > acceptance angle
- b. < critical angle d. < acceptance angle

28	The numerical aperture and cladding material	e of an optical fiber wi 1.30 is	ith c	ore material of refr	acti	ive index 1.55
a.	0.142	b. 0.254	c.	0.844	d.	0.562
29	The NA of an optical f. The NA of an optical f. of its core and cladding	fiber is 0.39 and the dig is 0.05, the refractive	ffere e inc	ence in refractive in lex of material of th	idic ne c	es of the material core is
a.	0.532	b. 1.521	c. 2	2.431	d.	0.254
30	. The NA for an optical 1.45 respectively is	l fiber with core and c	lado	ling refractive index	x be	eing 1.48 and
a.	0.1468	b. 0.5478	c. (0.0468	d.	0.2965
31	. The fundamental optic	cal parameter of an op	tical	l fiber is		
a.	Refractive index	b. Focal length c.	Opt	tical power d.	Nu	imerical aperture
32	. The light ray should the reflection to take place	ravel from medi	ium	to medium for	r to	tal internal
a.	Denser to denser	b. Denser to rarer	c	. Rarer to denser	(d. Rarer to rarer
33	Propagation of light th	rough fiber core is due	e to			
a.	Diffraction	b. Interference	C.	Refraction	(d. TIR
34	. The numerical apertur	re of a fiber is				
a.	a. A function of the fiber dimensions c. Independent on the refractive indices					
b. Dependent on the refractive indices of of the core and cladding						ing
	the core and cladding	5	d.	A function of leng fiber	gth	of the optical
35	. The refractive index o acceptance angle is	of core and cladding ar	re 1.:	50 and 1.44 respect	ive	ly and then
a.	23°.45'	b. 23°	c.	26°	(d. 24°.50'
36	The condition for prop.	agation of light in a fi	ber	is given by (θ=laun	ch a	angle)
a.	Sin θ=1	b. Sin θ >NA	C.	$\sin \theta X NA = 1$	(d. Sin $\theta < NA$
37	. The refractive index o	of a cladding of a fiber	wit	h core refractive ind	lex	1.5 and NA
		~ 23 ~				

0.244 is

a. 1.4	b. 1.325	c.	1.48	d. 1.656	
38.Optical fibers do not pick up electricity, because they are					
a. Transparent material		c.	Magnetic materials		
b. Non-metallic materi	als	d.	Electric materials		
39. The refractive indices of core and cladding of an optical fiber with a numerical aperture of 0.33 and their fractional difference of refractive indices being 0.02 are					
a. 1.65, 1.617	b. 1.325, 1.317	c.	1.48, 1.45	d. 1.656, 1.78	
40.An optical fiber has a numerical aperture of 0.20 and a cladding refractive index of 1.59. the acceptance angle for the fiber in water whose refractive index is 1.33 is					

a. 8°.39' b. 10° c. 26° d. 24°.50'

Problems on Fiber Optics

1. A glass fiber has core material of refractive index 1.466, cladding material of refractive index 1.46. If it is surrounded by air medium, compute the critical angle at the core-cladding interface.

Sol: Given that

The refractive index of core $n_1 = 1.466$

The refractive index of cladding $n_2 = 1.46$

We know that critical angle

$$\theta_c = \sin^{-1} \left[\frac{n_2}{n_1} \right]$$
$$\theta_c = \sin^{-1} \left[\frac{1.46}{1.466} \right] = 84.81$$

The critical angle at the core-cladding interface $\theta_c = 84.81$.

2. An optical fiber has a core material of refractive index of 1.55 and cladding material of refractive index 1.50. The light is launched into it in air. Calculate its numerical aperture.

Sol: Given that

The refractive index of core $n_1 = 1.55$

The refractive index of cladding $n_2 = 1.50$

$$NA = \frac{\sqrt{n_1^2 - n_2^2}}{n_0}$$

For air medium $n_0=1$

$$NA = \sqrt{n_1^2 - n_2^2}$$

= $\sqrt{1.55^2 - 1.50^2}$
= 0.39

The numerical aperture of an optical fiber, NA=0.39.

3. The numerical aperture of an optical fiber is 0.39. if the fractional refractive index change of the material of its core and cladding is 0.05, calculate the refractive index of the material of the core. Sol: Given that

The numerical aperture of an optical fiber, NA=0.39

Fractional refractive index change Δ =0.05

$$NA = n_1 \sqrt{2\Delta}$$
$$n_1 = \frac{NA}{\sqrt{2\Delta}} = \frac{0.39}{\sqrt{2x0.05}} = 1.233$$

The refractive index of the material of the core, $n_1=1.233$.

 Calculate the acceptance angle and the numerical aperture of a given optical fiber. If the refractive indices of core and cladding are 1.563 and 1.498 responsibility.
 Soly Given that

Sol: Given that

The refractive index of core $n_1 = 1.563$

The refractive index of cladding $n_2 = 1.498$

We know that the expression for Numerical aperture is

$$NA = \sqrt{n_1^2 - n_2^2}$$
$$= \sqrt{1.563^2 - 1.498^2} = 0.4461$$

The numerical aperture of an optical fiber, NA=0.4461

We know that the expression for Numerical aperture is

$$\sin \theta_c = \left(\sqrt{n_1^2 - n_2^2}\right) = NA$$
$$\theta_c = \sin^{-1}(NA)$$
$$\theta_c = \sin^{-1}(0.4461) = 26.49$$

The acceptance angle of the optical fiber $\theta c=26.49$.

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5. The numerical aperture of optical fiber is 0.2 when surrounded by air. Given the refractive index of the cladding is 1.59. Find the acceptance angle when the fiber is in water. Assume the f=refractive index of water as 1.33.

Sol: Given that

The numerical aperture of an optical fiber NA=0.2

The refractive index of cladding $n_2=1.59$

The refractive index of water $n_0 = 1.33$

We know that the numerical aperture of optical fiber is

$$NA = \frac{\sqrt{n_1^2 - n_2^2}}{n_0}$$

For air medium $n_0=1$, then

$$NA = \sqrt{n_1^2 - n_2^2}$$

$$n_1^2 = \sqrt{(NA)^2 + n_2^2}$$

$$= \sqrt{(0.2)^2 + (1.59)^2}$$

$$= 1.602$$

We know that the expression for acceptance angle

$$\theta_a = \sin^{-1} \left(\frac{\sqrt{n_1^2 - n_2^2}}{n_0} \right)$$
$$\theta_a = \sin^{-1} \left(\frac{\sqrt{(1.602)^2 - (1.59)^2}}{1.33} \right) = 8.46$$

The acceptance angle of the fiber in water $\theta_a = 8.46$

<u>UNIT – III</u>

Chapter – I: Crystallography

Chapter – II: X-Ray Diffraction

Course Outcome:

CO 3: Identify the crystal structures and XRD techniques. (K3).

APPLIED PHYSICS UNIT-III

CRYSTALLOGRAPHY

Introduction:

Matter is available in the universe in different forms; those are Solids, Liquids and Gases.

Solids: - A Solid consists of a large number of closely packed atoms or molecules. Solids are classified into two categories based on the arrangement of atoms. They are

1. Crystalline Solids

2. Amorphous solids

Crystalline Solids:-

In Crystalline Solids atoms or molecules are arranged in a regular manner. The Crystalline Solids have directional property; hence they are called as anisotropic substances.

Amorphous solids:-

In Amorphous solids atoms or molecules are arranged in a random manner. The Amorphous solids have no directional property; hence they are called as isotropic substances.



Crystal:-

Crystal is a transparent material, which has the regular periodic array of atoms.

Fundamental terms of Crystal structure:-

Space Lattice:- Space Lattice is nothing but a lattice, but it will have similar environment to see with reference lattice point is called **Space Lattice.**

Basis: - Lattice point with one or more atoms.

(or)

Group of atoms is called Basis

Unit cell: - The fundamental block of a crystal structure is known as **Unit Cell.**



Lattice parameters: - Lattice parameters are six in numbers. They are Three are Primitives and Three are inter axial / inter facial angles. a, b, c and α , β , δ are known as **lattice Parameters**. From these lattice parameters we can find out the external structural of the crystal.

Lattice: - The regular periodic array of atoms is called Lattice

Crystal Structure: - Lattice + Basis = **Crystal Structure.**

Crystallographic axis: - A line is drawn to touch the Three faces of unit cell is called **Crystallographic axis.**

Inter axial / Inter facial angles: - The angular inclination varies between crystallographic axis is called **Inter axial / Inter facial angles.**

Primitive cell or Simple cell: - The primitive cell is defined as a unit cell which contains lattice points at corners only. Such cell contains effectively one lattice point per cell i.e. one lattice point is associated with each primitive cell.

Non-primitive cell: - If a unit cell contains more than one lattice point then it is called Non-primitive cell (or) multiple cell.

Crystal systems and Bravasis Lattice:-

Crystals are classified into seven systems on the basis of the shape of the unit cell or lattice parameters, angles of the unit cell.

The seven crystal systems are classified in to 14 different types of unit cell. Those 14 types of systems are called Bravasis Lattice.

S.No	Crystal systems	Lattice parameters	Types of Bravasis Lattice	No. Of Bravasis Lattice	Figure
1.	Cubic	a=b=c α=β=δ=90°	P I F	3	
2.	Tetragonal	a=b≠c α=β=δ=90°	P I	2	
3.	Orthorhombic	a≠b≠c α=β=δ=90°	P I F C	4	
4.	Mono Clinic	$a\neq b\neq c$ $\alpha=\beta=90^{\circ}\neq\delta$	P C	2	
5.	Tri Clinic	a≠b≠c α≠β≠δ≠90°	Р	1	
6.	Rhombohedral 54,49,59, 64, 63	a=b=c α=β=δ≠90°	Р	1	\square

7.	Hexagonal	$a=b\neq c$ $\alpha=\beta=90^{\circ}$ $\delta=120^{\circ}$	Р	1	
Bravasis Lattice				14	

The classification of Bravasis lattice is based on the following crystal lattice

- 1. **Primitive Cell (P): -** In this lattice, the unit cell consists of eight corner atoms and all these corner atoms contributes only one effective atom.
- 2. Body Centered Lattice (I):- In addition to the eight corner atoms, it consists of an extra atom at the center of the body.
- **3.** Face Centered Lattice (F):- Along with corner atoms, each face will have one center atom.
- **4. Base Centered Lattice (C):-** Along with corner atoms, Base and opposite face will have center atom.

Crystal Structures:-

To study the Crystal Structures, we require to know some important parameters. They are

1. Effective number of atoms per unit cell (or) Number of atoms present in a unit cell:-

The effective number of atoms per unit cell is the total number of atoms considering the corner atoms, center atoms and face centered atoms.

2. Nearest neighboring distance(a):-

The distance between two nearest neighboring atoms is known as nearest neighboring distance.

3. Atomic Radius (r):-

Atomic Radius is the half of the distance between the atoms.
4. Coordination Number(N):-

The number of equidistant neighboring atoms is called Coordination Number.

5. Atomic Packing Factor(APF):-

Atomic Packing Factor is defined as the total volume occupied by the atoms in unit cell to the volume of the unit cell.

 $APF = \frac{\text{Total volume occupied by the atoms in unit cell}}{\text{volume of the unit cell}}$ $\frac{v}{V} = \frac{\text{No.of atoms present in a unit cell X volume of one atom}}{\text{volume of the unit cell}}$

6. Void Space:

The empty space available in a crystal lattice is called Void Space.

Simple Cubic Structure:

Simple cubic structure consists of 8 corners and 6 faces. All corners of the unit cell are touch with one another.



1. Effective number of atoms:-

The total number of atoms considering the corner atoms is called Effective number of atoms.

Total number of atoms and Corner atoms = $8X\frac{1}{g} = 1$

2. Nearest neighboring distance(a):-

The distance between two nearest neighboring atoms is known as nearest neighboring distance.

The nearest neighboring distance for Simple Cubic is

$$a = 2r$$

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3. Atomic Radius (r):-

Atomic Radius is the half of the distance between the atoms.

Atomic Radius r = a/2.

4. Coordination Number(N):-

The number of equidistant neighboring atoms is called Coordination Number.

Coordination Number for Simple cubic structure = 6

5. Atomic Packing Factor(APF):-

Atomic Packing Factor is defined as the total volume occupied by the unit cell to the volume of the unit cell.

$$\frac{v}{V} = \frac{\text{No.of atoms present in a unit cell X volume of one atom}}{\text{volume of the unit cell}}$$

$$v = \text{volume of one atom} = \frac{4}{3}\pi r^{3}$$

$$V = \text{volume of unit cell} = a^{3} = (2r)^{3} = 8r$$

$$\text{Number of atoms present in unit cell} = \frac{1}{8}X8 = 1$$

$$= \frac{\text{No.of atoms present in a unit cell X volume of one atom}}{\text{volume of the unit cell}} = \frac{1X\frac{4}{3}\pi r^{3}}{8r^{3}} = \frac{\pi}{6} \approx 0.52(or)52\%$$

Thus 52% of the volume of the simple cubic structure is occupied by the atoms. Hence it is loosely packed structure.

Body Centered Cubic Structure:

 $\frac{V}{V}$

Body centered cubic structure consists of 6 faces and 8 corners atoms along with one body centered atom. All corners atoms will be touch with one another via body centered atom.



1. Effective number of atoms:-

The total number of atoms considering the corner atoms and center atoms is called Effective number of atoms.

Total number of atoms and Corner atoms = $8X\frac{1}{8}+1=2$

2. Nearest neighboring distance(a):-

The distance between two nearest neighboring atoms is known as nearest neighboring distance.

consider
$$\Delta le \text{ ABD}$$

 $\Rightarrow \text{AB}^2 = \text{AD}^2 + \text{DB}^2 = a^2 + a^2 = 2a^2$
consider $\Delta le \text{ ABC}$
 $\Rightarrow AC^2 = AB^2 + BC^2$
 $(4r)^2 = 2a^2 + a^2$
 $16r^2 = 3a^2 \Rightarrow a^2 = \frac{16}{3}r^2 \Rightarrow a = \frac{4}{\sqrt{3}}r^2$



3. Atomic Radius (r):-

Atomic Radius is the half of the distance between the atoms.

Atomic Radius r =
$$r = \frac{\sqrt{3}}{4}a$$

4. Coordination Number(N):-

The number of equidistant neighboring atoms is called Coordination Number.

Coordination Number for Simple cubic structure = 8

5. Atomic Packing Factor(APF):-

Atomic Packing Factor is defined as the total volume occupied by the unit cell to the volume of the unit cell.

$$\frac{v}{V} = \frac{\text{No.of atoms present in a unit cell X volume of one atom}}{\text{volume of the unit cell}}$$
$$v = \text{volume of one atom} = \frac{4}{3}\pi r^{3}$$
$$V = \text{volume of unit cell} = a^{3} = (\frac{4}{\sqrt{3}}r)^{3}$$
$$\text{Number of atoms present in unit cell} = \frac{1}{8}X8 + 1 = 2$$
$$\sim 7 \sim$$

 $\frac{v}{V} = \frac{\text{No.of atoms present in a unit cell X volume of one atom}}{\text{volume of the unit cell}}$

$$=\frac{2X\frac{4}{3}\pi r^{3}}{\frac{64}{3\sqrt{3}}r^{3}}=\frac{\pi\sqrt{3}}{8}\approx 0.68(or)68\%$$

Thus 68% of the volume of the Body centered cubic structure is occupied by the atoms. Hence it is closely packed structure.

Face Centered Cubic Structure:

Face centered cubic structure consists of 8 corners and 6 faces along with six face centered atom.

1. Effective number of atoms:-

The total number of atoms considering the corner atoms and center atoms is called Effective number of atoms.

Total number of atoms and Corner atoms = $8X\frac{1}{8} + 6X\frac{1}{2} = 4$

2. Nearest neighboring distance(a):-

The distance between two nearest neighboring atoms is known as nearest neighboring distance.

consider
$$\Delta le \ ABC$$

 $\Rightarrow AC^2 = AB^2 + BC^2$
 $(4r)^2 = a^2 + a^2$
 $16r^2 = 2a^2 \Rightarrow a^2 = 8r^2$
 $\Rightarrow a=2\sqrt{2}r$



Atomic Radius is the half of the distance between the atoms.

Atomic Radius r =
$$r = \frac{a}{2\sqrt{2}}$$







4. Coordination Number(N):-

The number of equidistant neighboring atoms is called Coordination Number.

Coordination Number for Simple cubic structure = 12

5. Atomic Packing Factor(APF):-

Atomic Packing Factor is defined as the total volume occupied by the unit cell to the volume of the unit cell.

 $\frac{v}{V} = \frac{\text{No.of atoms present in a unit cell X volume of one atom}}{\text{volume of the unit cell}}$ $v = \text{volume of one atom} = \frac{4}{3}\pi r^{3}$ $V = \text{volume of unit cell} = a^{3} = (2\sqrt{2}r)^{3} = 16\sqrt{2}r^{3}$ Number of atoms present in unit cell = $\frac{1}{8}X8 + 6X\frac{1}{2} = 4$ $\frac{v}{V} = \frac{\text{No.of atoms present in a unit cell X volume of one atom}}{\text{volume of the unit cell}}$ $= \frac{4X\frac{4}{3}\pi r^{3}}{16\sqrt{2}r^{3}} = \frac{\pi}{3\sqrt{2}} \approx 0.74(or)74\%$

Thus 74% of the volume of the Face centered cubic structure is occupied by the atoms. Hence it is very closely packed structure.

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

1. ′	The number	of Lattice	points in a	a primitive cell is	
------	------------	------------	-------------	---------------------	--

a.	2	b. 3	c.	1	d.	4
2.	Highest packing fa	ctor occurs in				
a.	Body center cubic	crystal	c.	Diamond		
b.	Face center cubic	crystal	d.	Simple cubic cryst	als	
3.	The packing factor	is defined as the	rati	o of		
	a. The number of a	all atoms in the ur	nit c	cell to the volume o	f th	e unit cell
	b. The volume of t	he unit cell to the	nu	mber of atoms		
	c. The volume of t	he unit cell to the	vo	lume of all the atom	ns	
	d. The volume of	all atoms in the u	uni	t cell to the volum	e of	the unit cell
4.	The crystal system,	, which exhibits a	ll tł	e four types of stru	ictu	re, is
a.	Tetragonal	b. Cubic	c.	Hexagonal	d.	Orthogonal
5.	The number of atom	ns per unit cell in	the	e case of BCC, is		
a.	2	b. 1	c.	3	d.	4
6.	Coordination numb	per is the				
	a. Number of atom	ns per unit cell				
	b. Number of unit cell per unit volume					
	c. Number of nearest neighbours in a unit cell					
	d. Number of equ	idistant atoms in	n a '	unit cell		
7.	According to Brava	asis, total number	of	lattices are		
a.	11	b. 12	c.	13	d.	14

8.	The tiny fundam generates a cryst	nental block which, tal is called	when repeated in sp	pace in indefinitely			
a.	Primitive cell	b. Lattice cell	c. Unit cell	d. Simple cell			
9.	There are	- basic crystal syst	ems				
a.	Four	b. Five	c. Six	d. Seven			
10	. Effective numb	er of atoms belongi	ng to the unit cell o	f BCC structure is			
a.	8	b. 1	c. 2	d. 9			
11	. The coordinatio	on number of FCC s	tructure is				
a.	6	b. 8	c. 12	d. 4			
12	.The nearest neig	hboring distance in	the case of Simple	cubic structure is			
a.	$\frac{a}{\sqrt{2}}$	b. a	$c. a\sqrt{\frac{3}{2}}$	d. $a\sqrt{\frac{3}{4}}$			
13	. Atomic packing	g factor of FCC strue	cture is				
a.	0.68	b. 0.74	c. 0.52	d. 1.00			
14	There are of space called Bra	distinguishable way wasis lattices	s of arranging poin	t in three dimensional			
a.	7	b. 14	c. 8	d. 5			
15	In a crystal if the then it belongs t	e primitives a=b=c, o the system	and the interfacial	angles $\alpha = \beta = \gamma = 90^{\circ}$,			
	a. Cubic	b.Tetragonal	c. Mono clinic	d. Orthorhombic			
16	16.In a crystal if the primitives a=b=c, and the interfacial angles $\alpha=\beta=\gamma\neq90^{\circ}$, then it belongs to the system						
a.	Cubic I	b.Tetragonal	c. Trigonal	d. Orthorhombic			
17	17.In a crystal if the primitives $a=b\neq c$, and the interfacial angles $\alpha=\beta=\gamma=90^{\circ}$, then it belongs to the system						
a.	Cubic I	b.Tetragonal	c. Mono clinic	d. Orthorhombic			

18.1 t	In a crystal if the state of th	ne primitives a≠b≠c to the system	e, and the interfacial a	ingles α≠β≠γ≠90°,
8	a. Cubic	b. Triclinic	c. Monoclinic	d. Orthorhombic
19.	The element c	rystallizing in FCC	structure	
8	a. Copper	b. Sodium	C. Zinc	d. Diamond
20.	The coordinati	on number of BCC	structure is	
	a. 6	b. 8	c. 12	d. 4
21.	Atomic packir	ng factor of BCC str	ructure is	
	a. 0.68	b. 0.74	c. 0.52	d. 1.00
22.	The cubic stru	cture which has min	nimum value of pack	ing factor is
a. S	Simple cubic	b. BCC	c. HCP	d. FCC

X-RAY DIFFRACTION

Introduction:-

X- Rays are electromagnetic waves. The wavelength of X- Rays is of the order of $1A^{\circ}$.

- X- Rays are produced, when fast moving electron hit the target (or) material then it produces the radiation. These radiations are considered as X- Rays.
- X- Rays Diffraction is defined as bending of X- Rays around the obstacle.
- The X- Rays Diffraction occurs the size of the obstacle must be compared with the wavelength of radiation.
- X- Rays of wavelength is less than opaque obstacle it cannot produce X-Rays Diffraction.

Directions and Planes in Crystals:-

Crystals are the regular periodic array of atoms in 3-dimentional space. All these atoms fall by various directions in various planes of the crystal. These are known as Crystals Directions and Crystals Planes respectively.

In figure "O" is the origin and the directions are OA, OB, OC, and OD. The directions is described by giving the first inter point (XY) through which the line passes. The line OA is passing through the first point [X=1, Y=2], so the direction of OA is given by [12]. Similarly the directions OB, OC, OD are represented by [11], [32], [31].

The crystal planes are the planes which has highest lattice point on the planes. The lattice points forming space lattice may occupy various set of parallel planes.



Miller Indices:-

The set of parallel planes are represented by certain numbers is called as Miller Indices.

(**O**r)

There are smallest possible integers taken out of reciprocal of the intercepts made by crystal planes along three crystal axis.

Rules to find Miller Indices:-

- 1. Note intercepts made by the crystal planes along three crystal axis.
- 2. Take a coordinator of the intercepts made by the planes.
- 3. Find the inverse of the coordinates.
- 4. Multiplying with the LCM in order to have proper integer value.
- 5. Keep the value thus obtained in the parent.

i.
$$3a \ 2b \ 2c$$

ii. $3 \ 2 \ 2$
iii. $\frac{1}{3} \ \frac{1}{2} \ \frac{1}{2}$
iv. $\frac{1}{3}X6 \ \frac{1}{2}X6 \ \frac{1}{2}X6$
V (2 3 3)



- Miller Indices can be generally represented as (h k l)
- The crystal direction can be represented as [h k l]

Important points of Miller Indices:-

- 1. Miller Indices always represented as parallel planes in crystals.
- 2. Miller Indices of the parallel crystal planes would be one and same.
- 3. Any plane passing parallel to any of the crystal axis will leave an at infinity. Then the miller indices value will be taken as zero.
- 4. If (h k l) are the Miller Indices of a crystal planes than the crystallographic intercepts made by the planes can be taken as a/h, b/k, c/l.

5. Miller indices can be used to find the inter planner distance of separation between the crystal planes.

Inter planner distance of separation $d = \frac{a}{\sqrt{h^2 + k^2 + l^2}}$

6. The angular inclination between the crystal direction of $[U_1, V_1, W_1]$ and $[U_2, V_2, W_2]$ can be given as

$$\cos\theta = \frac{U_1U_2 + V_1V_2 + W_1W_2}{\sqrt{U_1^2 + V_1^2 + W_1^2}\sqrt{U_2^2 + V_2^2 + W_2^2}}$$

Distance of separation between successive (h k l) Planes:-

Here we shall derive an expression for the spacing between two parallel planes in a given crystal lattice. For Convenience, we shall take a simple unit cell in which coordinates axis are mutually perpendicular. Then we can use certain coordinates for calculating interplanner spacing.

In figure OX, OY and OZ are orthogonal axis. The origin is 'O'. Consider any set of crystal planes represented by miller indices (h k l), the reference plane passing through the origin "o", the next plane cutting the intercepts a/h, b/k, c/l on X, Y, Z axis respectively.

i.e
$$OA = a/h$$

 $OB = b/k$
 $OC = c/l$

 $\begin{array}{c} & & & \\ & & & & \\ & & & \\ & & & &$

A normal "ON" is drawn to the plane ABC from the origin. The length of this from the origin to the plane will be the interplanner separation.

Let α , β and δ is the angles made by On with X, Y and Z directions respectively.

$$\cos \alpha = \frac{ON}{OA} = \frac{d}{a/h}$$

$$\cos \beta = \frac{ON}{OB} = \frac{d}{b/k}$$

$$\cos \alpha = \frac{ON}{OC} = \frac{d}{c/l}$$
(1)

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The law of direction cosines is represented as

Substituting the values from equation (1) in equation (2)

$$\left[\frac{d}{a/h}\right]^2 + \left[\frac{d}{b/k}\right]^2 + \left[\frac{d}{c/l}\right]^2 = 1$$
$$d^2 \left[\frac{h^2}{a^2} + \frac{k^2}{b^2} + \frac{c^2}{l^2}\right] = 1$$
$$d^2 = \left[\frac{1}{\frac{h^2}{a^2} + \frac{k^2}{b^2} + \frac{c^2}{l^2}}\right]$$

The Interplanner distance of separation is given by $d = \frac{1}{\sqrt{\frac{h^2}{a^2} + \frac{k^2}{b^2} + \frac{l^2}{c^2}}}$

The above equation is known as general equation for interplanner separation for any set of planes. In Cubic system, as we know that a=b=c, then the expression becomes equal to

$$d = \frac{a}{\sqrt{h^2 + k^2 + l^2}}$$

Bragg's Law:-

Bragg's law is known as one of the fundamental law of crystal physics. This is being invented by W.H. Bragg and his son W.L. Bragg in the year 1913. This law is being awarded with Nobel Prize in the year 1915. This Bragg's law enables us to have the complete structure of crystal.

Consider a set of parallel planes PQ, RS, TU separated by a distance "d". Let AB and DE be the incident beam of X-Rays, BC and EF are the diffracted beam of X-Rays.



Let θ be the Braggs angle(Or) Glancing angle. Let BG and BH be the normal drawn to BE and EF respectively.

From figure we have $|GBE = \theta$, $|EBH = \theta$

The path difference between the diffracted beams of X-Rays can be given as

$$\Delta = \text{GE} + \text{EH} \qquad (1)$$
From the $\Delta le \text{ GBE } \neq \sin \theta = \frac{\text{GE}}{\text{BE}} = \frac{GE}{d}$

$$\Rightarrow \text{ GE} = \text{d} \sin \theta \dots \dots \dots (2)$$
Similarly from the $\Delta le \text{ EBH } \neq \sin \theta = \frac{\text{EH}}{\text{BE}} = \frac{EH}{d}$

$$\Rightarrow \text{ EH} = \text{d} \sin \theta \dots \dots \dots (3)$$

Substituting equation (2) and (3) in Equation (1)

$$\Delta = d \sin \theta + d \sin \theta$$

$$= 2d \sin \theta \dots (4)$$

The condition for the constructive interference of diffracted beam of X-Rays is equal to " $n\lambda$ "

$$\Delta = n\lambda \dots \dots (5)$$

From equation (4) and (5)

$2d \sin \theta = n\lambda$

The Bragg's Law states that "The Path difference between the diffracted light rays is an integral multiple of the Wavelength " λ ".

Limiting conditions for Bragg's law:-From Bragg's law $2d \sin \theta = n\lambda$ We know that $\sin \theta \le 1$ $\Rightarrow \frac{n\lambda}{2d} \le 1$ $\Rightarrow n\lambda \le 2d$ For first order diffraction n=1, $\Rightarrow \lambda \le 2d$

This is the limitation on wavelength of X-rays to diffraction

Important Crystal Planes of Cubic Crystal Systems:-

There are three important crystal planes in the cubic crystal system. They are (100), (110), (111). This can be represented as,

- 1. (100) Indices - (100) Intercepts - (a/h, b/k, c/l) For Cubic Unit Cell a=b=c=1 (1/1 1/0 1/0) = (1 $\alpha \alpha$) = (1 0 0)
- 2. (110) Indices - (110) Intercepts - (a/h, b/k, c/l) For Cubic Unit Cell a=b=c=1 (1/1 1/1 1/0) = (1 1 α) = (1 1 0)
- 3. (111) Indices - (111) Intercepts - (a/h, b/k, c/l) For Cubic Unit Cell a=b=c=1 (1/1 1/1 1/1) = (1 1 1)

4. (010) Indices - (010) Intercepts - (a/h, b/k, c/l) For Cubic Unit Cell a=b=c=1 (1/0 1/1 1/0) = (0 1 0)



5. (0 0 1) Indices - (0 0 1) Intercepts - (a/h, b/k, c/l) For Cubic Unit Cell a=b=c=1 (1/0 1/0 1/1) = (0 0 1)



- 6. (0 1 1) Indices - (0 0 1) Intercepts - (a/h, b/k, c/l) For Cubic Unit Cell a=b=c=1 (1/0 1/1 1/1) = (0 1 1)
- 7. (1 0 1) Indices - (1 0 1) Intercepts - (a/h, b/k, c/l) For Cubic Unit Cell a=b=c=1 (1/1 1/0 1/1) = (1 0 1)



→ (001)

8. (101)

The Miller Indices can be positive as well as negative. The negative Miller Indices can be represented as $(\bar{1} \ 0 \ 0)$

9. Indices - (123) Intercepts - $(\frac{1}{1} \ \frac{1}{2} \ \frac{1}{3})$ $(\frac{1}{1} X 6 \ \frac{1}{2} X 6 \ \frac{1}{3} X 6)$ (632)

10. Indices - (102)
Intercepts -
$$(\frac{1}{1}, \frac{1}{0}, \frac{1}{2})$$

(102)



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OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

23.A direction line is drawn through the origin and it passes through the first integer point given by x=2, y=3, z=2. Then its direction is represented by						
e. (223)	f. (322)	g. (232)	h. (222)			
24. The Miller ind	ices (h k l) represents	5				
a. A plane	b. System of planes	c. The direction	d. a set of parallel planes			
25.A plane paralle	25.A plane parallel to xy plane is represented by the Miller Indices					
a. (111)	b. (100)	c. (010)	d. (001)			
26.A plane cuts th along x, y, z di	26.A plane cuts the three axes at 5a, 5b and 5c, where a, b, c are lattice constants along x, y, z directions. Then the Miller indices of this plane					
a. (111)	b. (110)	c. (101)	d. (011)			
27.Let 'a' be the l separation for	attice constant of a c [111] planes is	ubic crystal then the	interplanner			
a. a	b. $a/\sqrt{2}$	c. $a/\sqrt{3}$	d. a/2			
28.The interplann 6 A° of a cubic	er separation for a se crystal is	t of planes [221] wh	ose lattice parameter is			
a. 2 A°	b. 1 A°	c. 3 A°	d. 6 A°			
29.X- rays are						
a. Electric waves	b. Magnetic waves	c. Electromag etic waves	n d. Mechanical waves			
30. The wavelengt	h of X-rays are nearl	y equal to				
a. 1 cm	b. 1 A°	c. 1 meter	d. 5000 A°			
31.X-ray diffracti	on is noticed with					
a. Plane grating	b. Single crystal	c. rubber	d. Glass			
space						

32. Bragg's Law is defined as

a.	$d \sin\theta = n\lambda$	b. d sin θ =(n+1/2) λ	c.	$2d \sin\theta = (n+1/2)\lambda$	d.	2d sinθ=nλ
	33. In Bragg's rela	tion 2d sin θ =n λ , the fa	ctor	n is called		
a.	Order of diffraction	b. Refractive index	c.	Bragg number	d.	Density of x-rays
	34.In Bragg's relat	tion 2d sin θ =n λ , the fac	ctor	d is called		
a.	Lattice parameters	b. Interplanner spacing	c.	Density of the material	d.	diameter
	35. Crystal directio	ons are represented by				
a.	123	b. (123)	c.	[123]	d.	<123>
	36. Miller indices	are used to specify				
a.	Structure of the material	b. Unit cell	c.	Planes and directions in the crystal	d.	Intensity of Bragg lines
	37. The Miller Ind	ices of the plane paralle	el to	x-axis is represented	d by	1
a.	(111)	b. (100)	c.	(011)	d.	(101)
	38. The radiations the crystal	that produces observab	ole c	liffraction as the they	7 pa	ss through
a.	γ-rays	b. visible rays	c.	X-rays	d.	α-rays
	39.The Miller indi- intercepts on th	ces of a plane in a cubi ree crystallographic ax	c cr es?	ystal are (121). What	t are	e their
a.	a, b, c	b. 2a, b, 2c	c.	∞ , 0, ∞	d.	a, 2b, c
	40. A beam of X-ra its first Bragg's separation of th	ays of wavelength $\lambda=1$, reflection is noticed at is reflection	.25 <i>ι</i> t θ=	A° is made to fall on 45°, what is the inter	a m plar	aterial and
a.	0.88 A°	b. 8.8 A°	c.	0.5 A°	d.	0.6 A°
	41. A monochroma	atic X-ray beam of way	ve le	ength 1.25 A° falls or	nas	set of planes

whose separation is 2.5 A°. calculate the maximum Bragg's reflections that can be observed in this case

- a. 1 b. 2 c. 3 d. 4
- 42.Different planes in a crystal are indicated by the same miller indices (h k l). this means the planes
- a. Are parallel and equidistant to each otherotherc. Inclined to each otherd. Intersect each other
- b. Are perpendicular to each other

Problems on XRD

1. Show that in a simple cubic lattice the separation between the successive lattice planes (100), (110) and (111) are in the ratio of 1:0.71:0.58.

Or

Calculate the ratio $d_{(100)}$: $d_{(110)}$: $d_{(111)}$ for a simple cubic structure.

Sol: Given that

The three planes are (100), (110) and (111)

We know that the expression for interplanar spacing for a cubic crystal

$$d_{(hkl)} = \left(\frac{a}{\sqrt{h^2 + k^2 + l^2}}\right)$$
$$d_{(100)} = \left(\frac{a}{\sqrt{1^2 + 0^2 + 0^2}}\right) = a$$
$$d_{(110)} = \left(\frac{a}{\sqrt{1^2 + 1^2 + 0^2}}\right) = \frac{a}{\sqrt{2}}$$
$$d_{(111)} = \left(\frac{a}{\sqrt{1^2 + 1^2 + 1^2}}\right) = \frac{a}{\sqrt{3}}$$

Hence
$$d_{(100)}: d_{(110)}: d_{(111)} = a: \frac{a}{\sqrt{2}}: \frac{a}{\sqrt{3}}$$

=1: $\frac{1}{\sqrt{2}}: \frac{1}{\sqrt{3}}$
= $\sqrt{6}: \sqrt{3}: \sqrt{2} = 1: \frac{1}{1.414}: \frac{1}{1.732}$

2. In a tetragonal lattice a=b=2.5A, c=1.8A. deduce the value of interplanar separation for planes given by (111).

Sol: Given that a=b=2.5A, c=1.8A

We know that the expression for interplanar spacing for any lattice

$$d_{(hkl)} = \frac{1}{\sqrt{\frac{h^2}{a^2} + \frac{k^2}{b^2} + \frac{l^2}{c^2}}}$$

$$d_{(111)} = \frac{1}{\sqrt{\frac{1}{(2.5)^2} + \frac{1}{(2.5)^2} + \frac{1}{(1.8)^2}}} = 1.26A^{\circ}$$

The interplanar separation for (111) planes is $d=1.26A^{\circ}$

3. Calculate the interplanar separation for a plane of simple cubic structure whose Miller indices are (321). Assume lattice constant as 4.2×10^{-10} meter.

Sol: Given that

Lattice constant $a = 4.2 \times 10^{-10}$ meter

We know that the expression for interplanar separation for a cubic structure

$$d_{(hkl)} = \left(\frac{a}{\sqrt{h^2 + k^2 + l^2}}\right)$$
$$d_{(321)} = \left(\frac{4.2x10^{-10}}{\sqrt{9 + 4 + 1}}\right) = \frac{4.2x10^{-10}}{\sqrt{14}} = 1.12x10^{-10}m$$

4. A beam of x-rays of wavelength 0.071 nm is diffracted by (110) plane of rock salt with lattice constant of 0.28 nm. Find the glancing angle for the second order diffraction.

Sol: Given that

Wavelength λ =0.0071 nm=0.071x10⁻⁹m

Miller indices of diffraction plane (hkl)=(110)

Lattice constant a=0.28nm=0.28x10-9 m

Diffraction order n-2

We know that the expression for interplanar spacing for a cubic crystal

$$d_{(hkl)} = \left(\frac{a}{\sqrt{h^2 + k^2 + l^2}}\right)$$
$$d_{(110)} = \left(\frac{0.28x10^{-9}}{\sqrt{l^2 + l^2 + 0^2}}\right) = \frac{0.28x10^{-9}}{\sqrt{2}} = 0.197x10^{-9}m$$
$$\sim 25 \sim$$

The Bragg's law is $2dsin\theta = n\lambda$

$$\sin \theta = \left[\frac{n\lambda}{2d}\right]$$
$$\theta = \sin^{-1}\left[\frac{n\lambda}{2d}\right]$$
$$\theta = \sin^{-1}\left[\frac{2x0.071x10^{-9}}{2x0.197x10^{-9}}\right] = \sin^{-1}(0.360) = 21.12$$

The glancing angle θ =21.12.

5. A beam of x-rays is incident on Nacl crystal with lattice spacing 0.282nm. Calculate the wavelength of x-rays if the first order Bragg's reflection takes place at a glancing angle of 8.35. Also calculate the maximum order of diffraction possible.

Sol: Given that

Glancing angle θ =8.35

Lattice spacing d=0.282 nm=0.282x10⁻⁹ m

Diffraction order n=1

We know that Bragg's law is $2d\sin\theta = n\lambda$

2 x
$$0.282x10^{-9}$$
 x sin (8.35) =1 x λ
 $\lambda = 0.0841x10^{-9}$ m=0.841x10⁻⁹m=0.0841A

Maximum order of Diffraction $n = \frac{2d\sin\theta}{\lambda}$

For maximum order of diffraction the Bragg's angle, $\theta=90^{\circ}$

$$n = \frac{2x(0.282x10^{-9})\sin 90}{0.841x10^{-10}} = 6.7$$

Maximum order diffraction, n=6

6. What is the glancing angle at which the third order reflection of X-rays of 0.79 A° wavelength can occur in a calcite crystal of 3.04×10^{-8} cm spacing?

Sol: Given that

Wavelength $\lambda = 0.79 \text{ A}^{\circ} = 0.79 \text{ x} 10^{-9} \text{ m}$

Lattice spacing $d=3.04 \times 10^{-8} \text{ cm}=3.04 \times 10^{-10} \text{ m}.$

Diffraction order n=3.

According to Braggs law, 2d $\sin\theta = n\lambda$

$$\sin \theta = \left[\frac{n\lambda}{2d}\right]$$
$$\theta = \sin^{-1}\left[\frac{n\lambda}{2d}\right]$$
$$\theta = \sin^{-1}\left[\frac{3x0.79x10^{-10}}{2x3.04x10^{-10}}\right] = \sin^{-1}(0.3898) = 22.942$$
Bragg's angle θ =22.942.

7. Monochromatic X-rays of wavelength 1.5A° are incident on a crystal face having an interplanar spacing of 1.6 A°. Find the highest order for which Bragg's reflection maximum can be seen.

Sol: Given that

Wavelength of X-rays $\lambda = 1.5 \text{ A}^{\circ} = 1.5 \times 10^{-10} \text{ m}$

Lattice spacing $d=3.04 \times 10-8 \text{ cm}=3.04 \times 10^{-10} \text{ m}$.

We know that Bragg's law is $2d\sin\theta = n\lambda$

$$n = \frac{2d\sin\theta}{\lambda}$$

For maximum order of diffraction the Bragg's angle, $\theta=90^{\circ}$

$$n = \frac{2x(1.6x10^{-10})\sin 90}{1.5x10^{-10}} = 2.133$$

Maximum order diffraction, n=2.

$\underline{UNIT} - IV$

Chapter – I: Electromagnetic fields

Chapter – II: Magnetic Properties

Course Outcome:

CO 4: Apply the magnetic materials in engineering field. (K3)

<u>APPLIED PHYSICS</u> <u>UNIT-IV</u>

ELECTRO MAGNETIC FIELDS

Introduction:-

Electro magnetic field theory is the study of fields produced by electric charges at rest (or) motion.

- Electro static fields are produced by static electric charges, while
- Magneto static fields are produced by electric charge moving with uniform velocity
- Both electric and magnetic fields are basically independent.
- If electric charges move with uniform velocity, these fields are time invariant (or) stationary.
- If electric charges move with non-uniform velocity, we have the time varying electric and magnetic fields.
- A time varying electric field produces a time varying magnetic field, in turn the time varying magnetic field produces a electric field.

The combined field of such mutually induced electric and magnetic fields is called the electromagnetic fields.

Gauss's Theorem:-

Statement:-

This theorem states that " the surface integral of the normal component of vector "A" taken over a closed surface "S" is equal to the volume integral of the divergence of vector "A" over the volume "V" enclosed by the surface "S".

i.e
$$\iint_{S} A.ds = \iiint_{V} div A dv = \iiint_{V} (\nabla \cdot A) dv$$

Proof:-

Consider a small cubicle volume element as shown in figure. We know that div.A represents the amount of flux diverging per unit volume and hence the flux diverging from the element of volume dv will be div.A.dV.



So, that the total flux coming out from the entire z^{μ} volume is given by

$$\iiint_V \operatorname{div} A \operatorname{dv} \dots \dots (1)$$

Now we consider a small element of area ds on the surface "S" as shown in figure. Let \hat{n} represents the unit vector drawn normal to area ds. It should be remembered that out word drawn (\hat{n}) normal on a surface is taken as positive. The flux of "A" through the surface element ds is given by

$$(A. \hat{n}) ds = A. ds$$

So, the flux through the entire surface "S" is given by

$$\iint_{S} A.ds \dots (2)$$

This must be equal to the total flux diverging from the whole volume "V" enclosed by the surface "S". Hence equation (1) and (2) we get

i.e
$$\iint_{S} A.ds = \iiint_{V} div A dv$$

This is the divergence of Gauss theorem

Stock's theorem:-

Statement:-

This theorem states that "The line integral of a vector field A around a closed curve is equal to the surface integral of the curl of A taken over the surface "S" surrounded by the closed curve.



Consider a surface "S" enclosed in a vector field "A" as shown in figure (a). The boundary of the surface "S" is enclosed curve PQR. The line integral of "A" around the curve PQR traced counter – clockwise is

i.e. $\oint_{c} A. dl$ (1)

Let the entire surface divided into a large number of square loops as shown in figure (b). Let the area enclosed by each infinitesimally small loop be "ds". Suppose \hat{n} be a unit positive outward normal (\hat{n}) upon ds. So, the line integral of "A" around the boundary of the area ds is curl A.ds.

This applied to all surface elements. Hence the sum of the line integral of "A" around the boundaries of the entire area element is given by

$$\iint_{s} curl \ A.ds \ \dots \ (2)$$

The sum of the line integrals on the boundary line of the curve is given by equation (2). This is also given by equation (1). Hence

i.e. $\oint_{c} A. dl = \iint_{s} curl A.ds$ This is known as Stock's theorem.

Fundamental Laws of Electromagnetism:-

1. Gauss Law of Electro Statics :-

Gauss Law is the converse of coulomb's law. From coulomb's law we can calculate electric field intensity for a given charge, while gauss law enables us to determine the charge by knowing electric field. This law states that "Total flux emerging out of a closed surface is equal to the net charge within the closed surface".

(Or)

The divergence of electric field vector is $1/\epsilon_0$ times the charge density

$$\oint E \, ds = \frac{q}{\varepsilon_0}$$

2. Gauss Law for Magneto Statics:-

In general magnetic lines of force are either closed curve goes off to infinity. Consequently the number of magnetic lines of force entering any arbitrary closed surface is exactly the same leaving it. It means that of the magnetic induction B across any closed surface is always zero.

$$\oint B \, ds = 0$$

3. Faraday's Law:-

The magnitude of the induced emf is directly proportional to the negative rate of variation of the magnetic flux linked with the circuit. If ϕ be the magnetic flux linked with the circuit at any instant "t" and "e" be the induced emf, then

$$e = -\frac{d\phi}{dt}$$
$$\oint E. dl = -\frac{d\phi}{dt}$$

This relation is also known as "Neumann's Law.

4. Ampere's Law:-

Ampere derived a relation between current I and the magnetic field "B". Ampere's law is similar to Gauss Law is useful in determining the magnetic field of current carrying conductor. This law states that "The line integral of magnetic field B about any closed path is equal to μ_0 times of the net current I flow through the area bounded by the curve".

$$\oint \mathbf{B} \cdot \mathbf{dl} = \mu_0 \mathbf{I}$$

Maxwell's Equations:-

Maxwell in 1862 formulated the basic laws of electricity and magnetism in the form of our fundamental equations. These equations are known as Maxwell's equations.

The Integral form of these equations are

The Differential form of these equations are

$1. \oint E \cdot ds = \frac{q}{\varepsilon_0}$	1. $\nabla \cdot \mathbf{E} = \frac{\mathbf{q}}{\varepsilon_0}$
$2. \oint B \cdot ds = 0$	$2. \nabla \cdot \mathbf{B} = 0$
3. $\oint E \cdot dl = -\frac{d\phi_{\rm B}}{dt}$	3. $\nabla X E = -\frac{d\phi_{\rm B}}{dt}$
4. $\oint \mathbf{B} \cdot \mathbf{dl} = \mu_0 \mathbf{I}$	4. $\nabla \mathbf{X} \mathbf{B} = \mu_0 \mathbf{I}$

First Maxwell's equation:-

The Integral form of these equations are	The Differential form of these equations are
$1 \oint E ds = \frac{q}{ds}$	1. $\nabla \cdot \mathbf{E} = \frac{\mathbf{q}}{\mathbf{P}}$
\mathcal{E}_0	${\cal E}_0$

This is also known as Gauss Law of Electro Statics. Gauss Law is the converse of coulomb's law. From coulomb's law we can calculate electric field intensity for a given charge, while gauss law enables us to determine the charge by knowing electric field. This law states that "Total flux emerging out of a closed surface is equal to the net charge within the closed surface.

Second Maxwell's equation:-

The Integral form of equation

The Differential form of equation

The Differential form of equation

 $2. \oint B \cdot ds = 0 \qquad \qquad 2. \nabla \cdot B = 0$

This is also known as Gauss Law for Magneto Statics. In general magnetic lines of force in general are either closed curve goes off to infinity. Consequently the number of magnetic lines of force entering any arbitrary closed surface is exactly the same leaving it. It means that of the magnetic induction B across any closed surface is always zero.

Third Maxwell's equation:-

The Integral form of equation

3.
$$\oint E \cdot dl = -\frac{d\phi_{\rm B}}{dt}$$
 3. $\nabla X E = -\frac{d\phi_{\rm B}}{dt}$

This is also known as Faraday's Law. The magnitude of the induced emf is directly proportional to the negative rate of variation of the magnetic flux linked with the circuit. If ϕ be the magnetic flux linked with the circuit at any instant "t" and "e" be the induced emf.

Fourth Maxwell's equation:-

The Integral form of equation	The Differential form of equation
4. $\oint \mathbf{B} \cdot \mathbf{dl} = \mu_0 \mathbf{I}$	4. $\nabla X B = \mu_0 I$

This is also known as Ampere's Law. Ampere derived a relation between current I and the magnetic field "B". Ampere's law is similar to Gauss Law is useful in determining the magnetic field of current carrying conductor. This law states that "The line integral of magnetic field B about any closed path is equal to μ_0 times of the net current I flow through the area bounded by the curve".

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

- 1. The electric field intensity is in the direction of the force F and is measured in
 - a. Newton's / Coulomb b. Meters c. Coulomb d. Newton's
- 2. Maxwell's first equation in differential form is
- 3. Maxwell's second equation in differential form is

4. Modified form of Ampere's law as suggested by Maxwell is

a.
$$\oint \vec{B} = \mu_0 \left[J + \varepsilon_0 \frac{\partial \vec{E}}{\partial t} \right]$$
 b.
$$\oint \vec{B} \cdot \vec{dl} = \mu_0 \left[J + \varepsilon_0 \frac{\partial \vec{E}}{\partial t} \right]$$
 c.
$$\oint \vec{B} \cdot dl = \mu_0 \left[J + \varepsilon_0 \frac{\partial \vec{E}}{\partial t} \right]$$
 d.
$$\oint \vec{B} = \mu_0 \left[J + \varepsilon_0 \frac{\partial \vec{E}}{\partial t} \right]$$

- 5. Emf is closed ------ integral of non-conservational electric field that is generated by battery
 - a. Line b. Surface c. Volume d. None
- 6. Maxwell's equation in----- form give information at points of discontinuity in electromagnetic fields
 - a. Differential **b. Integral** c. Algebric d. None
- 7. Ampere's Law is similar to ----- Law
- a. Lenz's **b. Gauss's** c. Biot-Savart's d. Faradays

8. Maxwell's third equation is derived from ----- Law

- a. Newton's b. Ampere's c. Biot-Savart's d. Faradays
- 9. As per Gauss's law, the total electric flux ϕ through a closed surface and the total charge q by that surface are related as ------

a.	$\phi = \sqrt{q_{enc}}$	b. $\phi = \frac{1}{\sqrt{q_{max}}}$	c. $\phi = \frac{1}{q_{enc}}$	d. $\phi = q_{enc}$
		V ¹ enc	1 enc	

- 10. As per strokes theorem, $\oint \vec{E}.\vec{dl} = ---$
 - a. ∞ **b.0** c. 1 d. None

MAGNETIC PROPERTIES

Introduction:-

The story of magnetic materials began with a mineral known as "Magnetite". This magnetite is available abundantly at a place called "Magnesia". The "magnet" comes from the word "Magnetite"

The materials which get magnetized in the presence of magnetic field are known as "Magnetic material". These materials are known to mankind from 800 B.C. But the actual development of magnetic material has taken place from 15th century efforts are due to scientist "Gilbert". The 19th century development efforts are due to "Orsted". According to him electric current will always be accompanied by magnetic fields, starting from the invention of compass box (mariners compass). These materials find wide and variety of applications in the field of science, engineering and technology.

Magnetism:-

The attracting property exhibited by the magnet.

Magnetic Dipole:-

The two ends are known as Magnetic poles and are called North Pole and South Pole.

If a system consisting of two equal and opposite magnetic poles separated by a distance "21".

Magnetic moment (µ_m):-

If "m" is the magnetic pole strength and "2l" is the length of the magnet, then its magnetic dipole moment is given by the product of "m" and "2l" is called Magnetic moment.

Magnetic field:-

The space surrounding the magnet up to which its attracting influence is felt is known as "Magnetic field".

Magnetic Induction (B) (or) Magnetic flux density:-

It is defined as the number of magnetic lines of force passing through a unit area of cross- section of magnetic materials.

$$B=\Phi/A - weber-m^2$$
 (or) Tesla

Magnetic field intensity (or) Magnetic field strength (H):-

It is the force experienced by a unit North Pole placed at a given point in a magnetic field.

Magnetic permeability (µ):-

Consider an unmagnetised bar of a magnetic material in a uniform magnetic field as shown in figure. It has been observed that the bar gets magnetized by induction and a polarity. After magnetization, the magnetic lines in the bar possess N-Pole throughout region and then re-enters to the south S-Pole as shown in figure (a). These lines from a closed loop within the magnet. By passing from S-Pole to N-Pole, that the lines of the magnetized bar opposes the lines of the original field outside the magnet and favor inside the magnet, the result is shown in figure (b).



As a result of this, the magnetic field strength (H) is increased inside the bar and decreased outside the bar. Similarly the magnetic flux (B) becomes high inside the bar and low outside the bar. Thus we find that flux density (B) is directly proportional to the magnetic field strength (H).

```
B \alpha H
i.e. B = \mu H \dots (1)\mu = B / H
```

Where " μ " is a constant proportionality and is known as "Absolute Permeability"

 $\sim 10 \sim$

If the flux density is established in air (or) vacuum (or) in a non- magnetic material, then the above equation can be written as

$$B_0 = \mu_0 H \dots (2)$$

 $\mu_0 = B_0 / H$

Where B_0 is the flux density in air (or) vacuum

 μ_0 is the absolute permeability of air (or) vacuum

Magnetic permeability of free space (μ_0) :-

It is defined as the ratio of magnetic induction (or) magnetic flux (B_0) of a free space to the applied magnetic field strength (H).

$$\mu_0 = B_0 / H$$

 $B_0 = \mu_0 H \dots (3)$
 $\mu_0 = 4\pi x 10^{-7} Hm^{-1}$

Relative permeability (µ_r):-

It is defined the ratio of permeability of a material to the permeability of free space.

i.e.
$$\mu_r = \mu / \mu_0$$

 $\mu = \mu_r \mu_0 \dots (4)$

Magnetization (M):-

Magnetization refers to the process of converting from unmagnetised bar into magnetized bar. (Or)

The magnetic moment per unit volume

Magnetic susceptibility (χ) :-

It is the ratio of the intensity of magnetization produced in the sample to the magnetic field intensity which produced the magnetization.

$$\chi = M / H$$
(5)
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Relation between Magnetic Induction (B), Magnetization (M), Relative permeability (μ_r), and Magnetic susceptibility (χ):-

We know that

$$B = \mu H$$

$$= \mu_0 \mu_r H$$

i.e.B = $\mu_0 \mu_r H + \mu_0 H - \mu_0 H$

$$= \mu_0 H + \mu_0 H (\mu_r - 1)$$

$$= \mu_0 H + \mu_0 M$$

$$B = \mu_0 (H + M) \text{ where } M = H(\mu_r - 1)$$

Where the magnetization M is equal to = H $(\mu_r - 1)$

i.e.
$$B = \mu_0 (H+M)$$
.

The first term on the right side of equation (5), is due to external field. The second term is due to magnetization.

Thus the magnetic induction (B) is a solid is $B = \mu_0 (H+M)$

$$\mu_0 = B / (H+M)$$

Relative Permeability $\mu_r = \mu / \mu_0$

$$=\frac{\frac{B}{H}}{\frac{B}{H+M}} = \frac{H+M}{H} = 1 + \frac{M}{H} \qquad \left(\because \chi = \frac{M}{H}\right)$$
$$\mu_r = 1 + \chi$$
Classification of Magnetic materials:-

Magnetic materials are broadly classified into two categories. Those are

- 1. Diamagnetic materials
- 2. Paramagnetic materials
- 3. Ferromagnetic materials

Diamagnetic materials:-

Materials composed of atoms or molecules, having zero magnetic moment are called diamagnetic materials



• When external magnetic field is applied it causes the magnetic moment of its atoms will align in the opposite direction of the applied field.

Properties:-

- 1. Permanent dipoles are absent.
- 2. The relative permeability (μ_r) of these materials is less than $1(\mu_r < 1)$, and susceptibility is (χ) is negative (- ve).
- 3. Diamagnetic materials are independent of temperature
- 4. When placed inside a magnetic field, magnetic lines of force are repelled.
- 5. The intensity of magnetization is negative.
- 6. No spin alignment is present.





magnetc field



Paramagnetic materials:-

If the paramagnetic materials have net magnetic moment, these magnetic moments are weakly coupled to each other.

- If the permanent dipoles do not interact with each other is called paramagnetic materials.
- When these are placed in a magnetic field, acquired feeble magnetism, the moment start to align, but only a small fraction is deflected into the field direction.

Properties:-

- 1. Paramagnetic materials posses' permanent dipoles.
- 2. The relative permeability (μ_r) of these materials is greater than $1(\mu_r>1)$, and susceptibility is (χ) is positive (+ ve).
- 3. paramagnetic materials are greatly depends on temperature
- 4. When placed inside a magnetic field, it attracts the magnetic lines of force.
- 5. The intensity of magnetization is positive (+ ve) and moderate.
- 6. The temperature "T" is less than Curie temperature, and then the material converted into diamagnetic material.

Ferromagnetic material:-

In ferromagnetic materials, the magnetic interaction between any two dipoles aligns themselves parallel to each other.

• Thus ferromagnetic substances posses' magnetic moment even in the absence of the applied magnetic field. This magnetization is known as "Spontaneous magnetization".







Properties:-

- 1. The ferromagnetic materials possess spontaneous magnetization.
- 2. The Relative permeability (μ_r) of these materials is very greater than $1(\mu_r >>1)$, value of susceptibility is (χ) is positive (+ ve) and very large.
- 3. The temperature below Curie temperature, the material would have ferromagnetic behavior. Temperature above Curie temperature the material is converted into paramagnetic material.
- 4. When placed inside a magnetic field, it attracts the magnetic lines of force very strongly.
- 5. In the presence of magnetic field, the magnetic lines of force are highly attracted towards the center of the material and hence, the magnetic field induction inside the material is very greater than the outside.

Depending upon the spin orientation the electrons, ferromagnetic materials are classified into two types. They are

- 1. Anti Ferro magnetic material
- 2. Ferri magnetic material

Anti Ferro magnetic material:-

The materials with anti- parallel magnetic moment (spin magnetic moment) are known as Anti Ferro magnetic materials.

In Anti Ferro magnetic materials, the magnetic interaction between any two adjacent dipoles align themselves anti parallel to each other. If the material is composed of atoms. One of the

atoms having their moment oriented in one direction and the other of atoms having their spin moments in the opposite direction as shown in figure.



Anti ferro magnetic material





Properties:-

- 1. Anti-Ferro magnetic materials posses' permanent dipoles.
- 2. The relative permeability (μ_r) of these materials is greater than $1(\mu_r > 1)$, and susceptibility is (χ) is positive (+ ve).
- 3. Anti-Ferro magnetic materials are greatly depends on temperature
- 4. When placed inside a magnetic field, it attracts the magnetic lines of force.
- 5. The temperature "T" is less than Curie temperature, and then the material converted into diamagnetic material.
- 6. The intensity of magnetization is positive (+ ve) and moderate.

Ferri magnetic materials:-

The substances which consist of anti-parallel magnetic moment of different magnitudes are known as Ferri magnetic substances.



magnetic material

(Or)

In Ferri magnetic materials, the magnetic interaction between any two adjacent dipoles, align themselves anti parallel to each other.

Properties:-

- 1. The Ferri magnetic materials possess spontaneous magnetization.
- 2. The Relative permeability (μ_r) of these materials is very greater than $1(\mu_r >> 1)$, value of susceptibility is (χ) is positive (+ ve) and very large.
- 3. The temperature below Curie temperature, the material would have ferromagnetic behavior. Temperature above Curie temperature the material is converted into paramagnetic material.
- 4. When placed inside a magnetic field, it attracts the magnetic lines of force very strongly.

5. In the presence of magnetic field, the magnetic lines of force are highly attracted towards the center of the material and hence, the magnetic field induction inside the material is very greater than the outside.

Hysteresis Loop:-

The hysteresis of Ferro magnetic materials refers to the lag of magnetization behind the magnetic field. It gives the relationship between the magnetic flux density (B) and magnetic field (H) referred as B-H curve.

Consider an unmagnetised ferromagnetic material is placed in a magnetic field. When the material is slowly magnetized and the magnetic flux density (B) increases with increase of magnetic field (H) initially through OA and reaches saturation at point 'A' known as "saturation magnetization (B_s)". When external magnetic field (H) is removed, the



magnetization slowly decreases but not comes to zero (at H=0), which is referred to as residual magnetization (B_r) at the point OB this phenomenon is called "retentivity". When reverse magnetic field is applied, the residual magnetism decreases and comes to zero for a particular value of reverse magnetic field known as coercive field (H_c) at the point OC and these phenomenon is called as "coercivity". After reaching the saturation level D, when the magnetizing field is reversed, the curve closes to the point A, completing the cycle. The loop OABCDEFA is called hysteresis loop as shown in figure.

The retentivity and coercivity are important characteristics of different ferromagnetic materials. Based on the degree of their values, the ferromagnetic materials may be classified as soft and hard magnetic materials.

Hard and soft magnetic materials:-

The magnetic materials are classified into two types.

- 1. Hard magnetic materials
- 2. Soft magnetic materials

Hard magnetic materials:-

The materials which are very difficult to magnetize and demagnetized are said to be hard magnetic materials.

Properties:-

- 1. Hard magnetic materials have large hysteresis loss due to large hysteresis loop area.
- 2. These materials have low value of susceptibility and permeability.
- 3. The coercivity and retentivity are large
- 4. These materials have large amount of impurities

Applications of Hard magnetic materials:

- 1. They are used in digital computers
- 2. They are used for making permanent magnets
- 3. They are used in transducers
- 4. They are used in magnetic tapes.

Soft magnetic materials:-

The materials which are easy to magnetize and demagnetized are said to be soft magnetic materials.



Properties:-

- 1. Soft magnetic materials have low hysteresis loss due to small hysteresis loop area.
- 2. These materials have large value of susceptibility and permeability.
- 3. The coercivity and retentivity are small
- 4. These materials are free from irregularities like strain and impurities.

Applications of Soft magnetic materials:

- 1. They are used in electromagnets.
- 2. They are used in AC current machinery.
- 3. They are used in communication equipment's.
- 4. They are used in audio and video transformers.

SUPER CONDUCTIVITY

Introduction:-

Resistance (or) resistivity is the property exhibits by thee materials. This is mainly due to the scattering of electrons, while interacting with positive ions present in the materials. When temperature of material is decreased to a low value, then due to lower energy, scattering of electrons decreases and as a result resistance (or) resistivity decreases. Then the conductivity increases.

The phenomenon of attains zero resistivity (or) infinite conductivity at low temperature is known as super conductivity.

The materials which exhibit superconductivity are known as super conductors.

Super conductivity was first observed by Kammerlingh onne's in the year 1911 in the case of \mathbb{R}^{Res}

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mercury. When temperature of mercury is decreases then the resistance also decreases and it is zero at 4.2 K temperature as shown in figure.

The temperature at which the material undergoes a transition from normal state to superconducting state is known as critical temperature (or) transition temperature.

Different materials have different T_c values

1.	Aluminium	Tc - 1.19 K
2.	Lead	Tc – 7.2 K
3.	Tungsten	$Tc - 0.01 \ K$
4.	Tin	Tc – 1.19 K
5.	Cadmium	Tc – 1.19 K

General properties:-

- 1. Super conductivity is a low temperature phenomenon
- 2. The transition from normal state to superconducting state occurs below the Critical Temperature(T_c).
- 3. Different materials will have different critical temperatures.
- 4. The current ones setup in a super conductor persists (stay) for a long time due to zero resistivity.
- 5. Super conductors do not aloe magnetic field through them and behaves as a dia magnetic material. This property of expulsion (repulsion) of magnetic field is known as " Meissner effect"
- 6. The magnetic field at which a super conductor loses its superconductivity and becomes a normal conductor is known as Critical Magnetic field (H_c).
- 7. Super conductivity occurs in metallic elements in which the number of valence electrons lies between 2 to 8.
- 8. Super conducting materials are not good conductors at room temperature

Meissner effect:-

Consider a normal conductor at room temperature as shown in Figure (a). When a magnetic field (H) is applied to it then it allows the magnetic lines to pass through it. Thus we have a magnetic induction field (B) in a conductor as shown in figure (b).



When the entire system is cooled so that $T < T_c$, then the normal conductor becomes a super conductor and it will not allow the magnetic lines to pass through it. It expels the magnetic lines. This effect, observed by Meissner, is known as "Meissner effect". Thus the superconductor does not allow the magnetic lines through it (or) expels the magnetic lines as shown in figure (c).

For a normal conductor, magnetic induction field "B" is given by

 $B = \mu_0 (H+M)$

Where μ_0 is the permeability of free space (or) air

M is the magnetization of the normal conductor

For a super conductor, B=0

 μ_0 (H+M) =0

H=-M

i.e. applied magnetic field induces magnetization in opposite direction

$$\chi = M / H = -1$$
$$\chi = -1$$

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Types of super conductors:-

In the presence of critical magnetic field, a super conductor converts into a normal conductor. Based on the conversion process, super conductors are classified into two types.

- 1. Type I super conductors
- 2. Type II super conductors

Based on diamagnetic response, super conductors can be classified as Type - I and Type – II super conductors.

The super conductors exhibit a complete Meissner effect (perfect dia magnetism) are called Type-I super conductors are also known as soft super conductors.

When the magnetic field strength is gradually increased from its initial value H<Hc at Hc, the diamagnetism abruptly disappear and the transition from super conducting state to normal sate is sharp as shown in figure(a).



Type –II superconductors are shown in figure (b), up to the field, the specimen is in a pure superconducting state. The magnetic flux lines are rejected. When the field is increased beyond H_{C1} (the lower critical field), the magnetic flux lines starts penetrating. The specimen is in a normal state. This means that the Meissner effect is incomplete in the region between H_{c1} and H_{c2} . This region is known as vertex state (or) mixed state. Type –II super conductors are known as hard super conductors.

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

11. The susceptibility	of diamagnetic mat	erial is	5			
a. Positive	b. Negat	tive	c. Zer	0	d. No	one
12. In ferro magnetic	material, the spin al	ignme	nt is			
a. Regular	b. Irregular	c. No a	alignment		d. No	one
13. The relation betw	een B and H is					
a. $B = \mu H$	b. Η = μ	ιB	c.	$\mu = BH$	d.	H= Bµ
14. The units of mag	netic susceptibility a	re				
a. Amp-m ²	b. Henry/m	c.	No units	d.	Ampe	ere m
15. The units of mag	netic dipole moment	are				
a. Amp-m	b.Amp-	m^2	c.	Amp/m	d.	Amp/m ²
16. The magnetism ex	xhibited by all mater	rials is				
a. Dia	b. Para		c.	Ferro	d.	Ferri
17. Spontaneous mag	netization is present	in				
a. Diamagnetic	b.Paramagnetic	c.	Ferroma	agnetic	d. Ar	ntiferro
18. The value of one	Bohr magneton is					
a. $9.273 \times 10^{-24} \text{ A-m}^2 \text{ b.}$	$9.273 \times 10^{24} \text{ A-m}^2$	c. 9.	273x10 ⁻²⁷	$A-m^2$ d	. 9.273x	10^{27} A-m^2
19. If the magnetic m	oment of atoms of a	mater	ial is zero,	the materi	al is cal	led
a. Diamagnetic b.	Paramagnetic	С	. Ferromag	gnetic	d. Ar	ntiferro
20. The units of relati	ive permeability is					
a. No units b.	Weber	С	. Tesla	d.	Amp	o/meter
21. Above curie temp	perature, a magnetic	materia	al becomes	5		
a. Diamagnetic b.	Paramagnetic	c . F	erromagne	etic d.	Anti	ferro

1.	The condition required for superconductivity phenomenon in a material is			
	a.	H=0, R=0, below T _c	c.	H≠0, R=0, above T_c
	b.	H=0, R=0, above T _c	d.	H≠0, R=0, below T_c
2.	Supe	rconductors are materia	ls	
	a.	Perfectly Ferro magnetic	c.	Perfectly Paramagnetic
	b.	Dielectric	d.	Perfectly Diamagnetic
3.	The r	magnetic susceptibility of a superc	onc	luctor is
	a1	b. +1	c.	0 d. ∞
4.	Persi	stent current is the characteristic p	orop	erty of
	a. Su	perconductor	c.	Josephson Effect
	b. Me	eissner Effect	d.	Hall Effect
5.	5. Magnetic induction is zero inside a superconductor is			
	a. M	eissner Effect	c.	Josephson Effect
	b. Ha	ll Effect	d.	Isotope Effect
6.	For T	Type –I superconductor		
	a. Tw	vo critical magnetic fields exist	C	e. Only one critical magnetic fields exist
	b. Tw	vo critical electric fields exist	Ċ	l. Only one critical electric fields exist
7.	For T	Type –II superconductor		
	a. Tv	vo critical magnetic fields exist		c. Only one critical magnetic fields exist
	b. Tw	vo critical electric fields exist		d. Only one critical electric fields exist
8.	Exan	nples of Type-I superconductors a	re	
	a. Al,	, Nb and Ta b. Al, Zn and Hg	c.	Ta, V and Nbd. Hg, Na and Zn

9. Below transition temperature, a superconducting material exhibits

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- a. Only zero resistance
- b. Only diamagnetic property
- 10. The magnetic of a superconductor is
 - a. 0 b. H c. 1
- 11. In a superconducting state
 - a. Entropy alone change
 - b. Electric specific heat alone change

c. Both entropy and electronic specific heat change

- d. Both remains constant
- 12. In Type-I superconductors the coherence length is of the order of
 - a. 10^6 m b. 10^{-3} m c. 10^3 m d. 10^{-6} m
- 13. When a material becomes superconductors

a. The properties of lattice structure do not change

- b. The properties of lattice structure do not change
- c. It becomes ferromagnetic in nature
- d. Magnetic property does not change
- 14. In superconducting state the energy gap
 - a. Is large compared to semiconductors and insulators
 - b. Is zero

c. Is very small as compared to semiconductors and insulators

d. Does not change

- c. Zero resistance and diamagnetism
- d. Zero resistance and ferromagnetism

d. -H

Problems on Magnetic Properties

1. Find the relative permeability of a ferromagnetic material id a field of strength 220 amp/m produces a magnetization of 3300 amp/m in it.

Sol: Given that

The field strength of ferromagnetic material if a field H= 220 amp/m Magnetization I=3300 amp/m

We know that the expression for relative permeability

$$\mu_r = 1 + \frac{I}{H}$$
$$= 1 + \frac{3300}{220} = 16$$

The relative permeability of a ferromagnetic material μ_r =16.

2. A magnetic material has a magnetization of 3300 amp/m and flux of 0.0044 weber/m². Calculate the magnetizing field and the relative permeability of the material. The permeability of vacuum is $4\pi x 10^7$ H/m. Sol: Given that

Magnetization of the material I=3300 amp/mThe flux densityB=0.0044 weber/m2The permeability of vacuum $\mu_0=4\pi x 10^7$ H/m.We know that the expression for magnetic flux density is

$$B = \mu_0 (H + M)$$

$$H = \frac{B}{\mu_0} - I$$

$$= \frac{0.0044}{4x3.142x10^7} - 3300 = 200 amp / m$$

And the expression for relative permeability is

$$\mu_r = 1 + \frac{I}{H} = 1 + \frac{3300}{200} = 17.5$$

The expression for magnetic flux density H=200 amp/m The relative permeability of the magnetic material μ_r =17.5

3. The magnetic field in the interior of a certain solenoid has the value of 6.5x10-4 T. when the solenoid is empty. When it is filled with iron, the field becomes 1.4T. Find the relative permeability of iron. Sol: Given that

The magnetic field of solenoid without iron $B_0=6.5 \times 10^{-4} \text{ T}$

The magnetic field of solenoid with iron B=1.4 T

We know that the expression for magnetic flux density, $B=\mu H$

$$B = \mu_0 \mu_r H \text{ and } B_0 = \mu_0 H$$
$$\mu_r = \frac{B}{B_0} = \frac{1.4}{6.5 \times 10^{-4}} = 2154.$$

$\underline{UNIT} - V$

Chapter – I: Quantum Mechanics

Chapter – II: Semiconductor Physics

Course Outcome:

CO 5: Identify the various applications of semiconductors in engineering field. (K3)

<u>APPLIED PHYSICS</u> <u>UNIT-V</u> QUANTUM MECHANICS

Introduction:-

The Classical Newtonian Mechanics explains the macroscopic system in which the particles are stationary (or) move with ordinary speed.

- The Classical Mechanics fails to explain a host experimental results of atomic phenomenon involving electron, proton etc, whose size and interacting distances are extremely small.
- Another difficult with classical theories is that they are formulated separately to particles and waves.
- So, physicists struggle continuous in search of most general and unified theory which can explain all macroscopic as well as microscopic systems.
- This has lead to the development of quantum theory, quantum mechanics and relativistic quantum mechanics also known as quantum field theory.

Quantum Mechanics is a branch of physics, which deals with the microscopic particles.

Ex: - A little sugar added to water in a glass, it dissolves without raising the water level.

The phenomenon like interference, diffraction, polarization of light etc is explained on the basis of wave nature of light.

On the other hand, photo electric effect, Compton Effect etc is explained on the basis of particle nature of light.

i.e. Radiation (or) light waves has "Dual nature"

Wave:-

A wave is nothing but spreading of disturbance in a medium. (or) propagation of energy by creating the disturbance in the medium is called wave.

Characteristics:-

- Amplitude
 Time Period
 Phase
- 3. Frequency 6. Intensity

Particle:-

If a certain amount of quantity occupies a certain space

Characteristics:-

- 1. Mass 4. Momentum
- 2. Velocity5. Energy

properties of Matter Waves.

- 1. Lighter is the particle, greater is the wavelength associated with it.
- 2. Smaller is the velocity of the particle, greater is the wavelength.
- 3. when v=0, then $\lambda = \dot{\alpha}$.

Debroglie's Hypothesis:-

According to Debroglie's

- 1. The entire universe is filled with matter and radiation.
- 2. As the radiation has dual nature, the matter should also exhibit dual nature. i.e. wave nature and particle nature.
- 3. The wave particle associated with wave is known as "Matter wave" (or) Debroglie wave.
- 4. The wavelength associated with the Matter particles is known as "Debroglie's wave length". This is the Debroglie's Hypothesis.

Derivation:-

According to Plank's quantum theory of radiation, the energy of the particle

E = hv	Where C is the velocity of light
$=\frac{hc}{2}$ (1)	λ is the wave length

According to Einstein mass energy relation $E = mc^2$ (2) From equation (1) and (2) $\frac{hc}{\lambda} = mc^2$ $\lambda = \frac{h}{mc}$(3) (wave nature)

If we have a particle of mass (m) travelling with a velocity (v) and has a momentum (mv), then Debroglie's wavelength associated with that particle

$$\lambda = \frac{h}{mv} \dots \dots \dots (4) \quad \text{(particle nature)}$$

$$\lambda = \frac{h}{mv} = \frac{h}{\sqrt{2meV}} = \frac{12.26}{\sqrt{V}} A^{T} \begin{bmatrix} K.E = 1/2mv^{2} \\ ev = 1/2mV^{2} \\ mv = \sqrt{2meV} \end{bmatrix} \begin{bmatrix} h = plank \text{ 's cons } \tan t = 6.625X10^{-34} \text{ } j \text{ / sec} \\ m = mass \text{ of electron} = 9.1X10^{-31} \text{ } kg \\ e = ch \arg e \text{ } of \text{ } electron = 1.602X10^{-19} \text{ } coulomb \end{bmatrix}$$

Schrodinger Time Independent Wave Equation:-

The Schrodinger's wave equation is the mathematical formulation of matter waves. This is being given by Schrodinger in the year 1930. This is also known as a fundamental wave equation of quantum mechanics. According to him matter wave can be given with a function known as $\psi(x)$.

The wave function on its own has no significance and represented the probability amplitude of the particle. But $|\psi(x)|^2$ has a physical significance and this represents the probability density.

Consider a material particle of mass "m" moving with a velocity "v" in the space. The general wave equation with particle can be given as

$$\psi(x) = A\sin\left(\frac{2\pi x}{\lambda}\right)....(1)$$

Where A is the amplitude

X is the position

 λ is the wave length

Differentiating twice of equation (1) w.r.to "x"

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But the Debroglie's wavelength associated with the material particle which is travelling with the velocity.

$$\lambda = \frac{h}{mv}.....(3)$$
$$\frac{1}{\lambda^{2}} = \frac{m^{2}v^{2}}{h^{2}} = \frac{2m\left(\frac{1}{2}mv^{2}\right)}{h^{2}}....(4)$$

But, the kinetic energy associated with the material particle, can be given as

$$K.E = \frac{1}{2}mv^{2}$$

$$E = K.E + P.E$$

$$K.E = E - V$$

$$E = K.E + P.E$$

Substituting equation (5) in equation (4)

Substituting equation (6) in equation (2)

This equation (7) and (8) is known as Schrodinger's wave equation.

$$\frac{\partial^2 \psi}{\partial x^2} + \frac{2m}{\hbar^2} (E - V) \psi = 0....(9) \qquad \therefore \hbar = \frac{h}{2\pi}$$

The three dimensional motion of the particles can be given from Schrodinger's equations of the form

~ 4 ~

$$\nabla^2 \psi + \frac{2m}{\hbar^2} (E - V) \psi = 0....(10)$$

Where Δ =Laplacian operator

$$\nabla^2 = \frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + \frac{\partial^2}{\partial z^2}$$
$$\therefore \frac{\partial^2 \psi}{\partial x^2} + \frac{\partial^2 \psi}{\partial y^2} + \frac{\partial^2 \psi}{\partial z^2} + \frac{8\pi^2 m}{h^2} (E - V) \psi = 0$$

Physical significance of a wave function $\psi(x)$:-

- 1. The wave function ψ has no direct physical meaning. It is a complex quantity represented the variation of matter wave. It connects the particle nature and its associated wave nature.
- 2. It can tell the probability of the position of the particle at a time, but it cannot predict the exact location of the particle at that time.
- 3. The probability of finding a particle in a particular volume $d\tau$ is given by

Probability(*P*) =
$$|\psi^*\psi| d\tau = |\psi^2| d\tau$$
 where $d\tau = dx dy dz$

4. When the particle present in a particular volume, the total probability of finding the particle where is unity.

$$i.e. \iiint \left| \psi \right|^2 dx \ dy \ dz = 1$$

Particle in a One-Dimensional Potential Box:-

Consider a particle of mass "m", charge "e" and moving with a velocity "V" in a one dimensional potential box of infinite height in the positive x-direction.

Let "v" be the potential energy of the particle.

- \blacktriangleright v=0 inside the Potential Box
- \blacktriangleright v= ∞ outside the Potential Box



Boundary conditions:-

- 1. v = 0 at $0 \le x \le L$
- 2. $v = \infty$ at $L \le x \le 0$

The motion of the particle inside the one dimensional Box can be described in terms of Schrodinger's wave equation.

$$\frac{\partial^2 \psi}{\partial x^2} + \frac{8\pi^2 m}{h^2} (E) \psi = 0....(1) \quad (\because V=0 \text{ at } o \le x \le L)$$
$$\frac{\partial^2 \psi}{\partial x^2} + K^2 \psi = 0....(2)$$
$$\therefore K^2 = \frac{8\pi^2 m}{h^2} (E) \dots (3)$$

The solution of the equation (2) can be given as $\psi(x) = A \sin Kx + B \cos Kx$(4)

Where A, B are constants K is a wave vector

In order to find the value of A and B, we make use of the boundary conditions

$$i.e.(i)\psi(x) = 0 \text{ at } x = 0$$

(ii) $\psi(x) = \infty \text{ at } x = L$(5)

Applying (1) boundary condition of equation (5) in equation (4), we get

0 = 0 + B $\implies B = 0$

Applying (2) boundary condition of equation (5) in equation (4), we get

$$0 = A \sin KL + 0$$

$$\Rightarrow A \sin KL = 0$$

$$KL = \pm n\pi$$

$$K = \pm \left(\frac{n\pi}{L}\right).....(6)$$

$$E = \frac{K^2 h^2}{8\pi^2 m}....(7)$$

From equation (3)

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The energy "E" can be given as

Substituting the value of "K" of equation (6) in equation (7) $E = \frac{n^2 h^2}{8mL^2}$(8)

The equation (8) represents the total energy of the particle, which is moving one dimensional potential Box.

Where h - Plank's constant, m - Mass, L - Width of the potential Box

If
$$n = 1$$
, $E_1 = \frac{h^2}{8mL^2}$
 $E_2 = \frac{h^2}{8mL^2} = 2^2 \cdot \frac{h^2}{8mL^2} = 4 \cdot \frac{h^2}{8mL^2} = 4E_1$
 $E_3 = \frac{h^2}{8mL^2} = 3^2 \cdot \frac{h^2}{8mL^2} = 9 \cdot \frac{h^2}{8mL^2} = 9E_1$

- : Basing on equation (8), the energy of the particle never can be equal to "zero"
- :. The energy of the particle always gets quantized.
- ... The total probability of particle is somewhere in the box must be unity.

$$\Rightarrow \int_{0}^{L} |\psi(x)|^{2} dx = 1$$

$$\Rightarrow \int_{0}^{L} A^{2} \sin^{2} \frac{n\pi x}{L} dx = 1$$

$$\Rightarrow A^{2} \int_{0}^{L} \frac{\left[1 - \cos \frac{2\pi nx}{L}\right]}{2} dx = 1$$

$$\Rightarrow \frac{A^{2}}{2} \left[x - \frac{L}{2\pi n} \cdot \sin \frac{2\pi nx}{L}\right]_{0}^{L} dx = 1$$

$$\Rightarrow \frac{A^{2} L}{2} = 1$$

$$\Rightarrow A^{2} = \frac{2}{l}$$

$$\Rightarrow A = \sqrt{\frac{2}{l}}$$

The normalized wave function $\psi_n = \sqrt{\frac{2}{l}} \sin \frac{n\pi x}{L}$

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

- 1. The velocity of matter waves depends on
- c. It is independent of particle velocity
- b. Velocity of particle

a. Velocity of waves

- 2. The equation of motion of matter waves was derived by -----
 - a. Heisenberg b. Bohr **c. De-Broglie** d. Schrodinger

d. None

3. The wavelength associated with a particle of mass 'm' moving with a velocity V is given by

a.
$$\lambda = \frac{h}{mv}$$
 b. $\lambda = \frac{hm}{v}$ c. $\lambda = \frac{hv}{m}$ d. $\lambda = \frac{m}{hv}$

- 4. De- Broglie wave are associated with ----
 - a. Moving neutral particle only c. All moving particle
 - b. Moving charged particle only d. All particles whether in motion or at rest
- 5. The De-Broglie wavelength of a particle of mass 'm' moving with kinetic energy E is ----

a.
$$\sqrt{\frac{h}{2mE}}$$
 b. $\frac{h}{2mE}$ c. $\frac{h}{\sqrt{2mE}}$ d. $\frac{\sqrt{h}}{2mE}$

6. According to De-Broglie, electrons exhibit which nature?

- a. Waveb. Particlec. Wave and particled. Energy7. If an electron is moving in a potential of 100V then the wavelength associated with it is --
- a. 1.225 cm b. **1.225** A° c. 1.225 m d. 12.25 A°
- 8. The Schrodinger time independent wave equation of a free particle is ------

a.
$$\frac{\partial^2 \psi}{\partial x^2} + \frac{2mE}{\hbar^2} \psi = 0$$

b.
$$\frac{\partial^2 \psi}{\partial x^2} + \frac{2m}{\hbar^2} \psi = 0$$

c.
$$\frac{\partial \psi}{\partial x^2} + \frac{2mE}{\hbar^2} \psi = 0$$

d.
$$\frac{\partial^2 \psi}{\partial x^2} + \frac{\hbar^2}{2m} (E - V) \psi = 0$$

- 9. Wave function must be ----
 - a. Finite every where b. Continuous
- 10. Energy of the particle in a potential box
 - a. $\frac{n^2 h^2}{8mL^2}$ b. $\frac{h^2}{8mL^2}$ c. $\frac{h^2}{8mL^2}$ d. $\frac{n^2 h^2}{2mL^2}$

c. Single valued

d. All the options

SEMICONDUCTOR PHYSICS

Origin of energy band formation in solids:-

The atoms in solids are held together by inter atomic force (or) bond. When the attractive force and repulsive force between any two atoms are equal, the two

atoms occupy a stable position with a minimum potential energy. The spacing between the atoms is called equilibrium spacing.

The electrons of a single atom occupy atomic orbitals, which forms a discrete set of energy levels. If several atoms brought together to form a molecule, their atomic orbitals are splits due to the Pauli's exclusive principle. This produces a



number of molecular orbitals proportional to the number of atoms. When a large number of atoms are brought together to form a solid, the number of orbitals became excluding large with forbidden energy gap between them is illustrated in the figure for sodium metal.

The Na atom contains (11) eleven electrons having the electronic configuration $1S^2 2S^2 2P^6 3S^1 3P^0$ at 0°K, the lower band is partially filled with one electron known as the valence band (VB). The upper band is empty and known as conduction band (CB). The gap between the two is forbidden energy gap ΔE , which distinguish the metals, semi-conductors and insulators.

Classification of materials into Conductors, Semiconductors and Insulators:-

Conductors:-

Definition: - The material which passes electric current freely through them is called as conductors.

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- In case of conductors there is no forbidden band, the valence band and conduction band overlap each other. Hence plenty of free electrons are available for electric conduction.
- The electrons from valence band enter in the conduction band. Due to overlapping of valency band and conduction band a slight potential difference across the conductor cause the free electrons to constitute electric current.
- In metals the conductivities are of the order of 10^7 Ohm-m.

Semiconductor:-

Definition: - The material which can pass electric current partially through them is called as semiconductors.

- In Semiconductor the forbidden band is very small.
- Semiconductor materials are one whose electric property lies insulators between and good conductors.
- At 0°K, the valence band is completely filled and there are no electrons in conduction band. When a small amount of energy is supplied, the electrons can easily jump from valency band to conduction band.

Insulators:-

Definition: - The material that does not allow any electric current to pass through them is called as Insulators.

- In case of Insulators, the forbidden energy band is very wide. Due to this energy cannot jump from valency band to conduction band.
- For example, in case of materials like glass the valency band is completely fill at 0°K and the energy







Band]



gap between valence band and conduction bands is of the order of 10 eV.

• Even in the presence of high electric field, the electrons do not move from valency band to conduction band.

Intrinsic and Extrinsic semiconductors:

Depending on the purity and impurity of semiconductor it can be classified into two types.

- 1. Intrinsic semiconductor (or) Pure semiconductors
- 2. Extrinsic semiconductors (or) Impure semiconductors

Extrinsic semiconductors is of two types, they are

- 1. P Type semiconductors
- 2. N Type semiconductors

Intrinsic semiconductor:-

Intrinsic semiconductors are those in which impurities are not present and are called as pure semiconductors (or) intrinsic semiconductors.

Highly pure semiconductors are called intrinsic semiconductors

(Or)

Ex: - Germanium, Silicon.

Mechanism:-



To understand the electrical conduction in intrinsic semiconductor, let us consider the case of silicon. The atomic number of silicon is 14. It has 4 electrons in the outermost orbit. i.e. it is a Si atoms is shared by the valence electrons of four adjacent Si atoms and make four electrons pairs as shown in figure.

Extrinsic semiconductor:-

The Extrinsic semiconductors are those in which impurities of large quantity are present.

- The impurities can be either III group element (or) V group elements.
- These are classified into two types
 - 1. N Type Semiconductors
 - 2. P-Type Semiconductors

N-Type Semiconductors:-

When a pentavalent element is doped into an intrinsic semiconductors then four valence electrons of impurity atoms form four covalent bond with four intrinsic atoms and fifth electrons is left free.

- This electrons is free to move anywhere in the crystal and is known as conduction electron, which is denoted by pentavalent impurity.
- Hence V group elements are known as donor impurity.
- The number of electrons is more than the number of holes in N-Type semiconductor.
- Hence electrons are majority charge carriers.

P-Type Semiconductors:-

When an trivalent impurity is doped into an intrinsic semiconductor then the three valency electrons of impurity atoms make three covalent bonds with three intrinsic atoms and in the forth



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bond one position is vacant as intrinsic atom is supposed to make fourth covalent bond.

- Hence, trivalent impurities are known as accepter impurity.
- The number of holes is more than the number of electrons in the P-Type semiconductor.
- Hence, holes are the majority charge carriers and electrons are the minority charge carriers.

Hall Effect:-

When a magnetic field is applied perpendicular to the current carrying conductor, then a voltage is developed in the material perpendicular to both magnetic field and current in the conductor. This effect is known as Hall Effect. The voltage developed is known as hall voltage (V_H) .



Hall Effect is useful to identify the nature of charge carriers in a material and hence we can decide the material in N-Type (or) P-Type semiconductor.

To explain Hall Effect, consider a rectangular block of semiconductor in which current is flowing along the positive (+ve) X-direction and magnetic field "B" is applied along Z-direction as shown in figure.

As the charge carriers are moving in a magnetic field experience a force called Lorentz force. $E = B_{\rm e} V$ (1)

 $F_L = BeV....(1)$

Due to this Lorentz force, if the material is n-type semiconductor then electron will be deposited at face-1 and if the material is P-Type semiconductor then holes will be deposited at the face-2.

A potential difference, force is developed across face (1) and face (2) causing a field F_{H} . This field gives rise to a force.

 $F_H = eE_H....(2)$

At equilibrium

$$F_{H} = F_{L}$$

$$eE_{H} = BeV$$

$$E_{H} = BV.....(3)$$

If "J" is current density, then $J = n_e V$

Where n is the concentration $V = \frac{J}{n_e}$(4) of charge carriers. Substitute equation (4) in equation (3)

$$\therefore E_H = \frac{BJ}{n_e}....(5)$$

For a given semiconductor, the hall field E_H is proportional to the current density "J" and the intensity of magnetic field "B" in the material.

i.e
$$E_H \alpha JB$$

 $\therefore E_H = R_H JB$(6)
($\therefore R_H = Hall \ coefficient$]
have
 $\frac{BJ}{ne} = R_H JB$
 $R_H = \frac{1}{n_e}$(7)

Equation (5) and (6) we have

Generally for N-Type semiconductor, Hall Effect is developed in negative direction, negative (-ve) $R_H = -\frac{1}{n_e}$(8) sign is used

Similarly for P-Type semiconductor

$$R_H = \frac{1}{p_e}....(9)$$

 $\sim 14 \sim$

Determination of Hall coefficient:-

If "d" is the width of sample across which Hall voltage $V_{\rm H}$ is measured. Then

$$E_{H} = \frac{V_{H}}{d}$$
$$\therefore V_{H} = d.E_{H}$$
$$\therefore V_{H} = R_{H}BJd$$

If "t" is the thickness of the sample, then its cross section is d.t and current density can be written as

$$J = \frac{I}{d \cdot t}$$
$$\therefore V_{H} = \frac{R_{H} \cdot B \cdot I \cdot d}{d \cdot t} = \frac{R_{H} B I}{t}$$
$$\therefore R_{H} = \frac{V_{H} t}{IB}$$

Applications of Hall Effect:-

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- 1. The sign of charge carriers is determined.
- 2. The carriers concentration (number of charge carriers per unit volume) can be determined.
- 3. The mobility of charge carriers is measured directly.
- 4. Electrical conductivity of the material can be determined.
- 5. From the knowledge of measured Hall Voltage, the in known magnetic field provided the value of Hall coefficient is known.

OBJECTIVE QUESTIONS FOR ONLINE EXAMINATION

- 1. A germanium atom contains
 - a. Four protons
- b. Only two electron orbits
- 2. When atoms are held together by sharing of valence electrons
 - a. They form a covalent bond c. Each share electron leaves a electron
 - b. Each atom becomes free to move d. None
- 3. An intrinsic semiconductor at the absolute zero temperature
 - a. Behaves like an insulator c. Number of holes is equal to holes
 - b. Behaves like a conductor d. None
- 4. When voltage is applied to an intrinsic semiconductor which is at room temperature
- a. Electrons moves to the positive terminal and holes moves to the negative terminal
- b. Electrons moves to the negative terminal and holes moves to the positive terminal
- c. Both electrons and holes moves to the positive terminal
- d. Both electrons and holes moves to the negative terminal
- 5. When temperature of an intrinsic semiconductor is increased
- a. Resistance of the semiconductor increases c. Holes are created in the conduction band
- b. Heat energy decreases the atomic radius d. Energy of the atoms is increased
 - 6. The movement of a holes is brought about by
 - a. The vacancy being filled by a free electron

b. The vacancy being filled by a valence electron from a neighboring atom

- c. The movement of an atomic core
- d. None

c. Four valence electrons

d. Five valence electrons

7. Donor impurities

- a. Creates excess holes
- b. Can be added to germanium, but not to silicon

c. Must have only five valence electrons

- d. Must have only three valence electrons
- 8. Acceptor impurities
 - a. Creates excess holes
 - b. Can be added to silicon, but not to germanium
 - c. Must have only five valence electrons

d. Must have only three valence electrons

- 9. The forbidden energy gap in semiconductors
 - a. Lies just below the valence band
 - b. Lies just above the conduction band

c. Lies between the valence band and a conduction band

- d. Is the same as conduction band
- 10. In N-type semiconductor, the majority carriers are
 - a. Holes **b. Electrons** c. Holes and electrons d. None
- 11. In P- type semiconductor, the majority carriers are
 - **a. Holes** b. Electrons c. Holes and electrons d. None

Problems on Quantum Mechanics

1. Calculate the wavelength associated with an electron with energy 2000 eV. Sol: Given that

The energy of an electron E=2000 eV

The expression for wavelength of an electron in terms of energy is

 $\lambda = \frac{h}{\sqrt{2mE}}$

Where h is a Plank's Constant = $6.626 \times 10-34$ J-S

M is the mass of the electron = $9.1 \times 10-31$ Kg Substituting the values we get

$$\lambda = \frac{6.626 \times 10^{-34}}{\sqrt{2 \times 9.1 \times 10^{-31} \times 2000 \times 1.6 \times 10^{-19}}} = 0.2745 \times 10^{-10} m = 0.2745 A^{\circ}$$

The wavelength of an electron λ =0.2745A°

2. Calculate the wavelength associated with an electron raised to a potential of 54V. Sol: Given that

The potential applied to an electron V=54 V

The expression for wavelength of an electron in terms of potential is

$$\lambda = \frac{12.27}{\sqrt{V}} = \frac{12.27}{\sqrt{54}} = 0.167nm$$

The wavelength of an electron λ =0.167 nm

Calculate the De-Broglie wavelength associated with a neutron moving with a velocity of 2000m/s. (mass of the neutron m= 1.67x10⁻²⁷ Kg, Planck's constant h=6.626x10⁻³⁴ J-S). Sol: Given that

The velocity of neutron v=2000ms⁻¹

The mass of the neutron m= $1.67 \times 10^{-27} \text{Kg}$

Planck's constant h=6.626x10⁻³⁴ J-S

The expression for Debroglies wavelength is $\lambda = \frac{h}{mv}$

Substituting the values then we get

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$$\lambda = \frac{6.626 \times 10^{-34}}{1.67 \times 10^{-27} \times 2000} = 1.984 \times 10^{-10} = 1.984 \text{ A}^{2}$$

The wavelength of the electron λ =1.984A°

 An electron is bound in one dimensional infinite well of width 1x10-10m. Find the energy value of an electron in the ground state and first two excited states. Sol: Given that

> Length of the potential box $L=1\times10^{-10}$ Quantum states n=1, 2 and 3.

In one dimensional potential box, the energy corresponding to the nth quantum state is

$$E_n = \frac{n^2 h^2}{8mL^2}$$

For ground state n=1

$$E_{1} = \frac{h^{2}}{8mL^{2}}$$

$$E_{1} = \frac{\left(6.626 \times 10^{-34}\right)^{2}}{8 \times 9.1 \times 10 - 31 \times (1 \times 10^{-10})^{2}} = 0.603 \times 10^{-17} J$$

$$= \frac{0.063 \times 10^{-17}}{1.6 \times 10^{-19}} eV = 37.68 eV$$

For first energy state n=2
$$E_2 = \frac{4h^2}{8mL^2} = 4E_1 = 4x37.68 = 150.75eV$$

For Second energy state n=3

$$E_3 = \frac{9h^2}{8mL^2} = 9E_1 = 9x37.68 = 339.12eV$$

The values of the electron in the ground state and first excited states are $E_1=37.68$ eV, $E_2=150.75$ eV and $E_3=339.12$ eV.

 Calculate the energy required to jump an electron from ground state to the second excited in a metal. Sol: Given that

In one dimensional potential box, the energy corresponding the nth quantum state

$$E_n = \frac{n^2 h^2}{8mL^2}$$

is

Ground state energy $E_1 = \frac{h^2}{8mL^2}$ Second excited state energy $E_3 = \frac{9h^2}{8mL^2}$

The required energy $E=E_3-E_1$

$$E = \frac{9h^2}{8mL^2} - \frac{h^2}{8mL^2} = \frac{h^2}{mL^2}$$

Calculate the energy (in eV) required to jump an electron from ground state to the second excited state in a metal of length 10⁻¹⁰m.
 Sol: Given that

The length of metal $L=10^{-10}$ m

The planks constant $h=6.626 \times 10^{-34} \text{ J/S}$

Mass of the electron $m=9.1 \times 10^{-31} \text{Kg}$

The expression for energy corresponding to nth quantum state $E_n = \frac{n^2 h^2}{8mL^2}$ is

For second excited state n=3
$$E_3 = \frac{9h^2}{8mL^2}$$

 $E_3 = \frac{9(6.626 \times 10^{-34})^2}{8 \times 9.1 \times 10^{-31} \times (10^{-10})^2} = 5.427 \times 10^{-17} J$

The energy required to jump the electron from ground state to second excited state is $E_3=338.806$ eV.
Problems on Semiconductor Physics

1. The Hall coefficient of specimen is $3.66 \times 10^{-4} \text{ m}^3 \text{C}^{-1}$. Its resistivity is $8.93 \times 10^{-3} \Omega \text{m}$. Find i). Carrier density. ii)Mobility of charge carriers.

Sol: Given that

The hall coefficient of specimen $R_H=3.66 \times 10-4 \text{ m}^3 \text{C}^{-1}$. The resistivity of specimen $\rho=8.93 \times 10-3 \Omega \text{m}$ Charge of an electron= 1.6×10^{19} coulomb

The expression for Hall coefficient $R_H = \frac{1}{n_e}$

Then
$$n_e = \frac{1}{R_H e}$$

 $n_e = \frac{1}{R_H e} = \frac{1}{3.66 \times 10^{-4} \times 1.6 \times 10^{-19}} = 1.78 \times 10^{22} / m^3$

The mobility of an electron in terms of Hall coefficient is

$$\mu_e = \sigma_n R_H = \frac{R_H}{\rho_n} = \frac{3.66 \times 10^{-4}}{8.93 \times 10^{-3}} = 0.4099 \times 10^{-1} m^2 / V - S$$

The carrier density of electron density of electron $n=1.78 \times 10^{22}/m^3$ The mobility of charge carriers $\mu e=0.4099 \times 10^{-1} m^2/V$ -S